

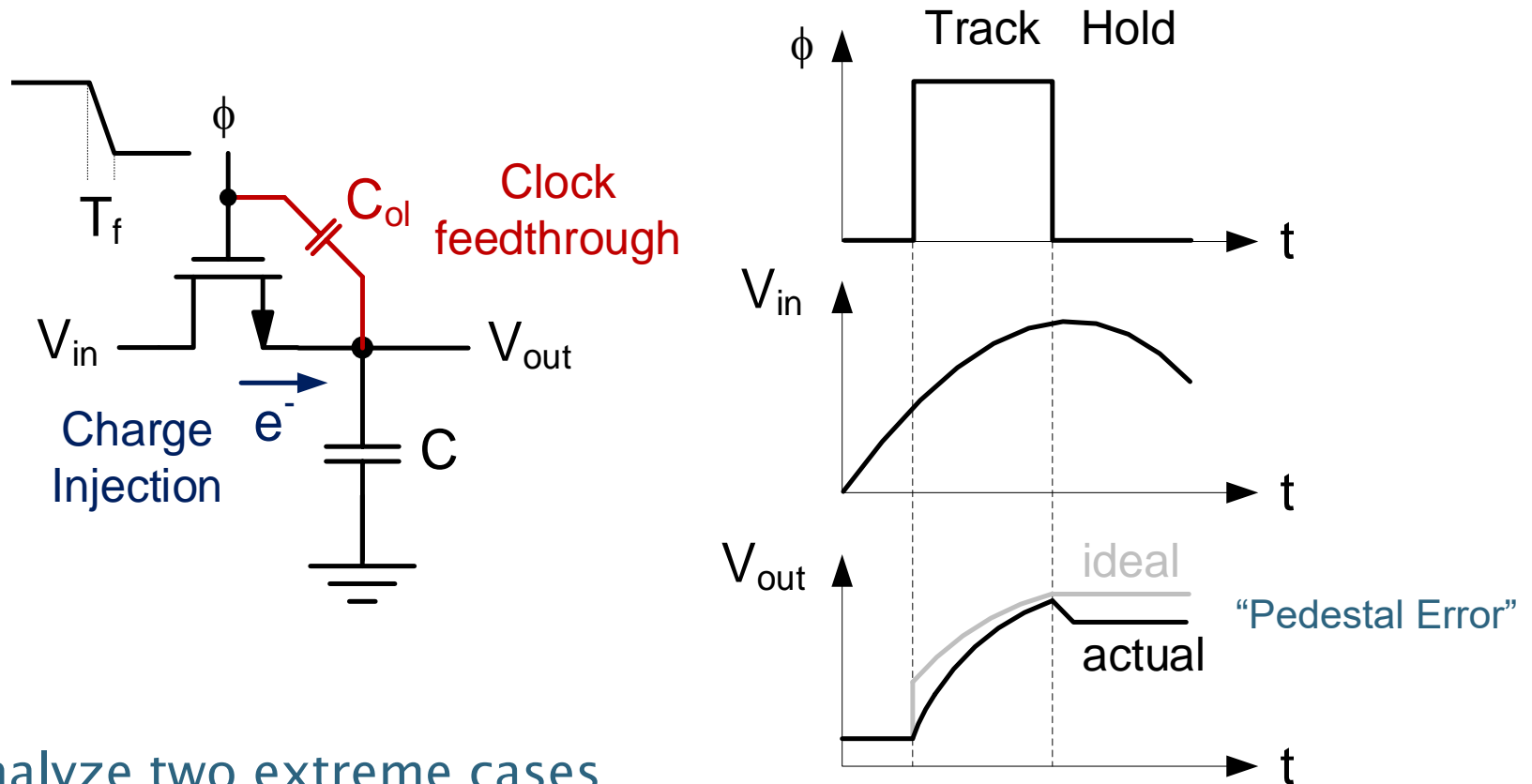
# **EE 240C**

## **Analog-Digital Interface Integrated Circuits**

### **Track & Hold Amplifier**

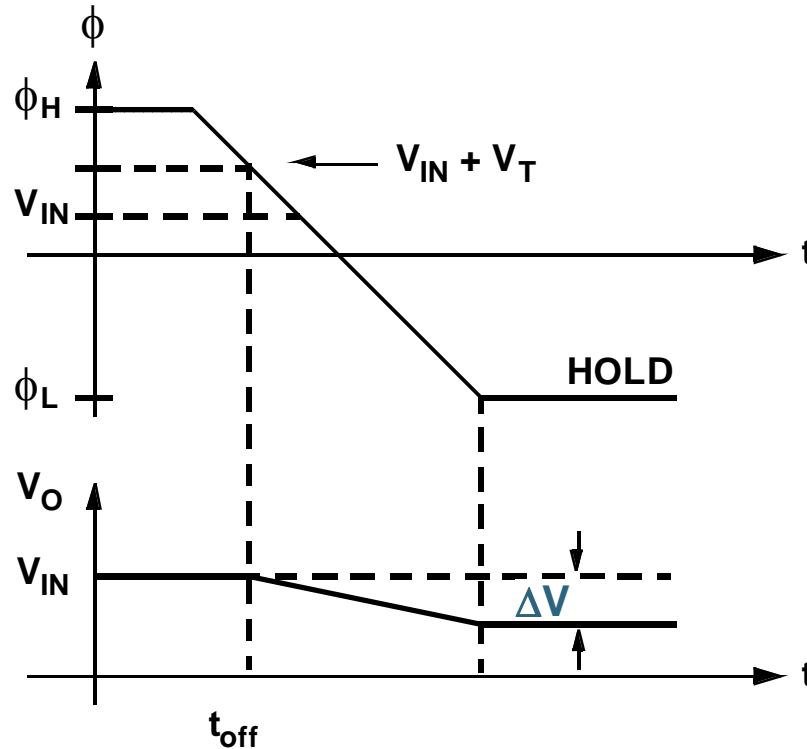
### **Switch Charge Injection**

# Charge Injection and Clock Feedthrough



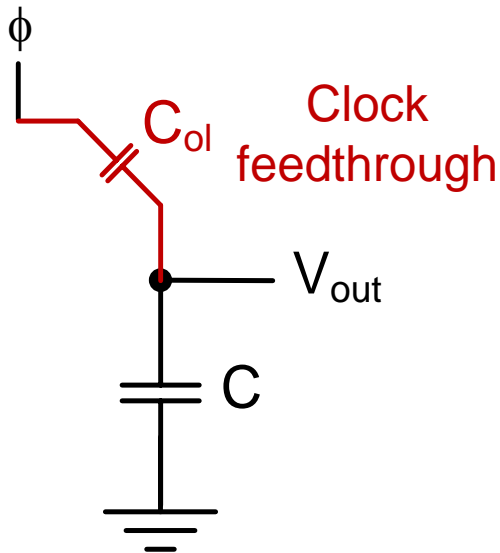
- Analyze two extreme cases
  - Very large  $T_f$  ("slow gating")
  - Very small  $T_f$  ("fast gating")

# Slow Gating



- All channel charge has disappeared by  $t_{off}$  without introducing error; it is absorbed by the input source

# Slow Gating Model for $t > t_{\text{off}}$



$$V_{\text{out}} = V_{\text{in}} - \Delta V_{\text{out}}$$

$$V_{\text{out}} = V_{\text{in}} - \frac{C_{\text{ol}}}{C_{\text{ol}} + C} (V_{\text{in}} + V_t - \phi_L) = V_{\text{in}}(1 + \varepsilon) + V_{\text{os}}$$

$$\varepsilon = -\frac{C_{\text{ol}}}{C_{\text{ol}} + C}$$

Gain Error

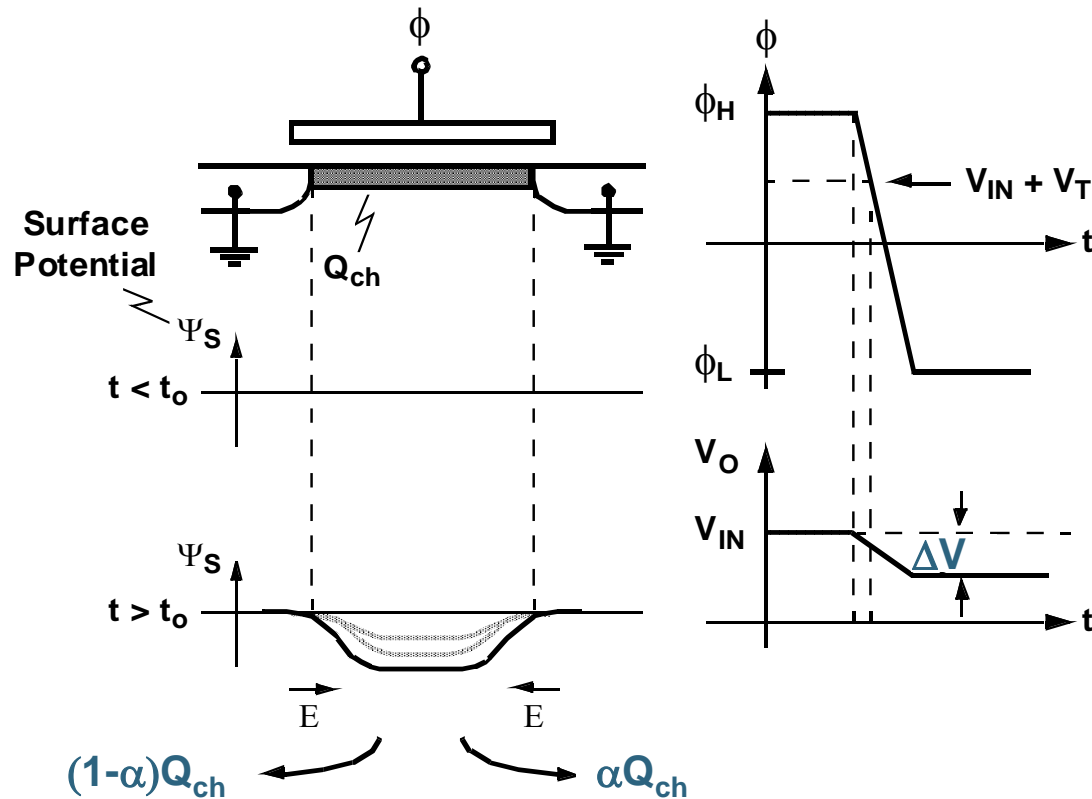
$$V_{\text{os}} = -\frac{C_{\text{ol}}}{C_{\text{ol}} + C} (V_t - \phi_L)$$

Offset Error

- Example:  $C = 1\text{pF}$ ,  $\phi_L = 0\text{V}$ ,  $V_t = 0.45\text{V}$ ,  $W = 20\mu\text{m}$ ,  $C_{\text{ol}}' = 0.1\text{fF}/\mu\text{m}$ ,  $C_{\text{ol}} = 2\text{fF}$

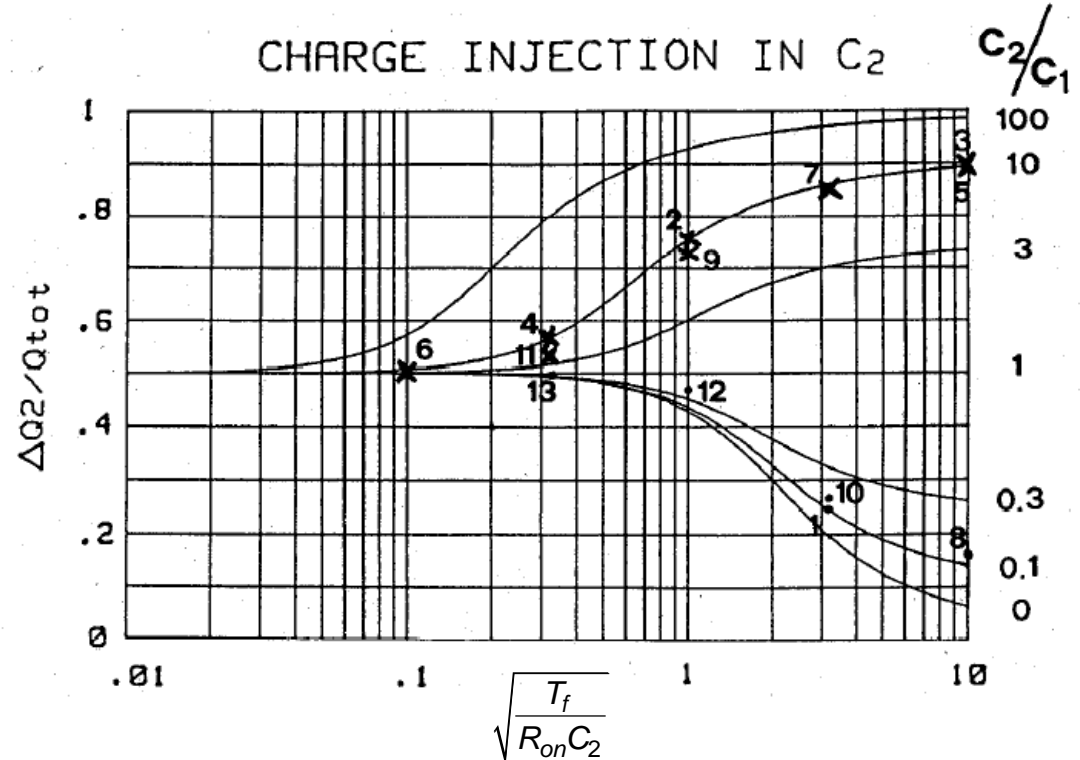
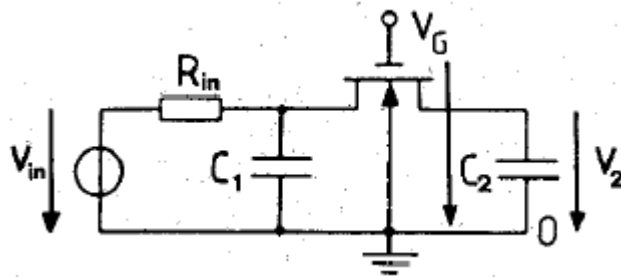
$$\varepsilon = -0.2\% \quad V_{\text{os}} = -0.9\text{mV}$$

# Fast Gating



- Channel charge cannot change instantaneously
- Resulting surface potential decays via charge flow to source and drain
- Charge divides between source and drain depending on impedances loading these nodes

# Charge Split Ratio Data



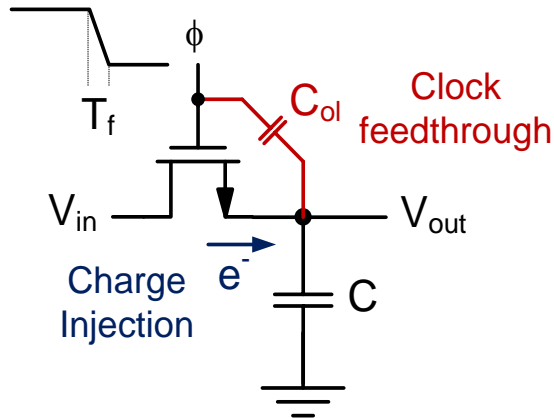
- G. Wegmann et al., "Charge injection in analog MOS switches," IEEE J. Solid-State Circuits, pp. 1091–1097, June 1987.
- Y. Ding and R. Harjani, "A universal analytic charge injection model," Proc. ISCAS, pp. 144–147, May 2000.

# Interpretation

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- $R_{on}C_2$  and  $T_f$  are usually comparable, or at least not more than an order of magnitude apart
  - This brings us into the range of 0.1...1 on the chart by Wegmann
- This means that the charge split will in practice have some dependence on the impedances seen on the two sides of the transistor
- Remember: Slightly more charge will go to the side with lower impedance

# Fast Gating Model for $t > t_{\text{off}}$



$$V_{\text{out}} = V_{\text{in}} - \Delta V_{\text{out}} = V_{\text{in}}(1 + \varepsilon) + V_{\text{os}}$$

$$V_{\text{out}} = V_{\text{in}} - \frac{C_{\text{ol}}}{C_{\text{ol}} + C}(\phi_H - \phi_L) + \frac{1}{2} \frac{Q_{\text{ch}}}{C} \quad \text{Assuming 50/50 charge split}$$

$$Q_{\text{ch}} = -WLC_{\text{ox}}[\phi_H - V_{\text{in}} - V_t]$$

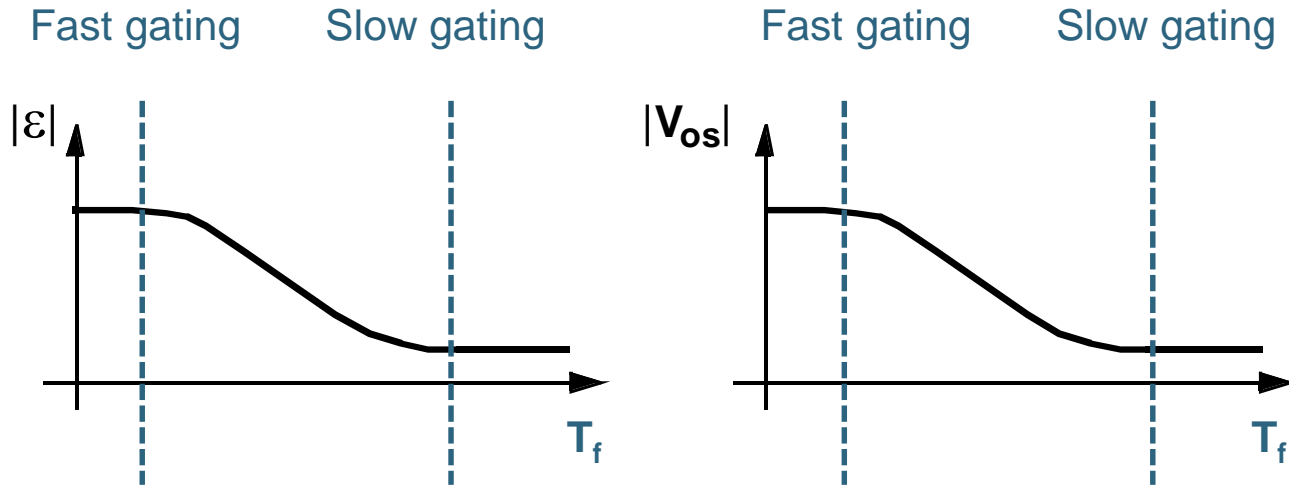
$$\varepsilon = \frac{1}{2} \frac{WLC_{\text{ox}}}{C} \quad V_{\text{os}} = -\frac{C_{\text{ol}}}{C_{\text{ol}} + C}(\phi_H - \phi_L) - \frac{1}{2} \frac{WLC_{\text{ox}}}{C}(\phi_H - V_t)$$

- Example:  $C=1\text{pF}$ ,  $\phi_H - \phi_L = 1.8\text{V}$ ,  $V_t = 0.45\text{V}$ ,  $W=20\mu\text{m}$ ,  $LC_{\text{ox}}=2\text{fF}/\mu\text{m}$ ,  $C_{\text{ol}}'=0.1\text{fF}/\mu\text{m}$ ,  $C_{\text{ol}}=2\text{fF}$

$$\varepsilon = +2\% \quad V_{\text{os}} = -30.6\text{mV}$$



# Transition Fast/Slow Gating



- $|\epsilon|$  and  $|V_{os}|$  decrease as the fall time of  $\phi$  ( $T_f$ ) increases and approach the limit case of slow gating
- Unfortunately, high-speed switched capacitor circuits tend to operate in fast gating regime

# Impact of Technology Scaling

$$\left. \begin{aligned} \Delta V &\cong \frac{1}{2} \frac{Q_{ch}}{C} \quad \frac{1}{2f_s} = \frac{T_s}{2} = N \cdot RC \\ R &\cong \frac{1}{\mu C_{ox} \frac{W}{L} (V_{GS} - V_t)} = \frac{L^2}{\mu Q_{ch}} \end{aligned} \right\} \boxed{\frac{\Delta V}{f_s} \cong N \frac{L^2}{\mu}}$$

- Charge injection error to speed ratio benefits from shorter channels and increases in mobility (e.g. due to strain)

# **EE 240C**

## **Analog-Digital Interface Integrated Circuits**

### **Track & Hold Amplifier – Improvements**

# Outline

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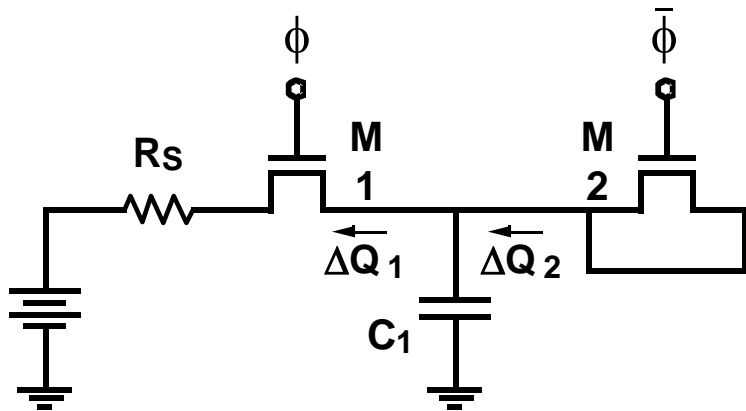
- Elementary track-and-hold circuit and its nonidealities
- First order improvements to elementary track-and-hold
- Advanced techniques
  - Clock bootstrapping
  - Bottom plate sampling
- Settling and noise analysis in charge-redistribution track-and-hold circuit
- Noise simulation example

# Improvements

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- Charge cancelation
  - Try to cancel channel charge by injecting a charge packet with opposite sign
- Differential sampling
  - Use a differential circuit to suppress offset
- CMOS switch
  - Try to balance the nonidealities of NMOS device with a parallel PMOS

# Charge Cancellation



$$L_2 = L_1$$

$$W_2 = 0.5W_1$$

$$\Delta Q_1 = 0.5Q_{ch1} + Q_{ol1}$$

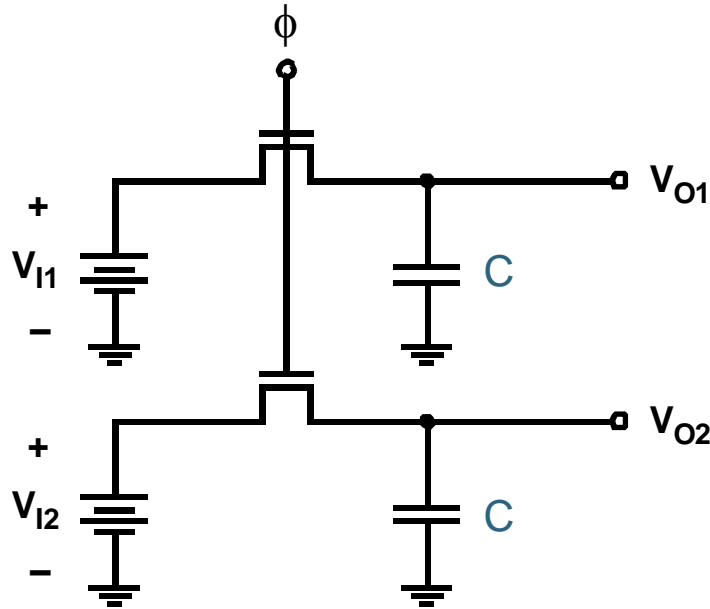
$$\Delta Q_2 \cong Q_{ch2} + 2Q_{ol2} \cong 0.5Q_{ch1} + Q_{ol1}$$

$$\Delta Q_1 - \Delta Q_2 \cong 0$$

[C. Eichenberger and W. Guggenbuhl, "[Dummy transistor compensation of analog MOS switches](#)," *IEEE J. Solid-State Circuits*, vol. 24, no. 4, pp. 1143-1146, Aug. 1989.]

- Cancellation is never perfect, since channel charge of M1 will not exactly split 50/50
  - E.g. if  $R_s$  is very small, most of M1's channel charge will flow toward the input voltage source
- Not a precision technique, just an attempt to do a partial clean-up

# Differential Sampling (1)



$$V_{ID} = V_{I1} - V_{I2}$$

$$V_{OD} = V_{O1} - V_{O2}$$

$$V_{IC} = \frac{V_{I1} + V_{I2}}{2}$$

$$V_{OC} = \frac{V_{O1} + V_{O2}}{2}$$

$$V_{O1} = (1 + \varepsilon_1)V_{I1} + V_{OS1}$$

$$V_{O2} = (1 + \varepsilon_2)V_{I2} + V_{OS2}$$

$$V_{OD} = \left(1 + \frac{\varepsilon_1 + \varepsilon_2}{2}\right)V_{ID} + (\varepsilon_1 - \varepsilon_2)V_{IC} + (V_{OS1} - V_{OS2}) \cong \left(1 + \frac{\varepsilon_1 + \varepsilon_2}{2}\right)V_{ID}$$

$$V_{OC} = \left(\frac{\varepsilon_1 - \varepsilon_2}{4}\right)V_{ID} + \left(1 + \frac{\varepsilon_1 + \varepsilon_2}{2}\right)V_{IC} + \left(\frac{V_{OS1} + V_{OS2}}{2}\right) \cong \left(1 + \frac{\varepsilon_1 + \varepsilon_2}{2}\right)V_{IC} + \left(\frac{V_{OS1} + V_{OS2}}{2}\right)$$

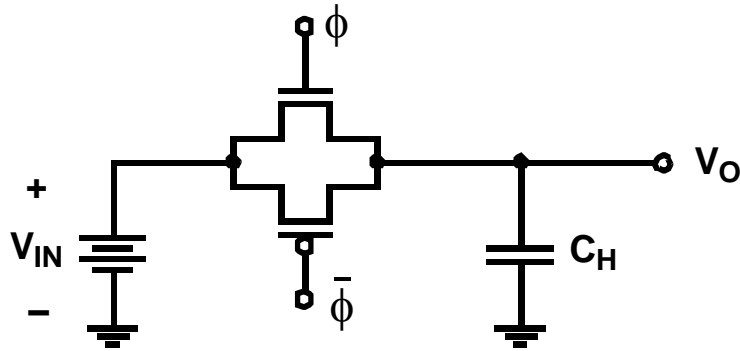
# Differential Sampling (2)

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- Assuming good matching between the two half circuits, we have
  - Small residual offset in  $V_{OD}$
  - Good rejection of coupling noise, supply noise, ...
  - Small common-mode to differential-mode gain
- Unfortunately,  $V_{OD}$  has essentially same gain error as the basic single ended half circuit
- This also means that there will be nonlinear terms
  - Our simplistic analysis assumed that the channel charge is linearly related to  $V_{in}$
  - This is true only to first order (consider e.g. backgate effect)
    - Expect to see nonlinear distortion along with gain error



# CMOS Switch



$$Q_{chn} \cong -W_n L_n C_{ox} (\phi_H - V_{IN} - V_{tn})$$

$$Q_{chp} \cong W_p L_p C_{ox} (V_{IN} - \phi_L - |V_{tp}|)$$

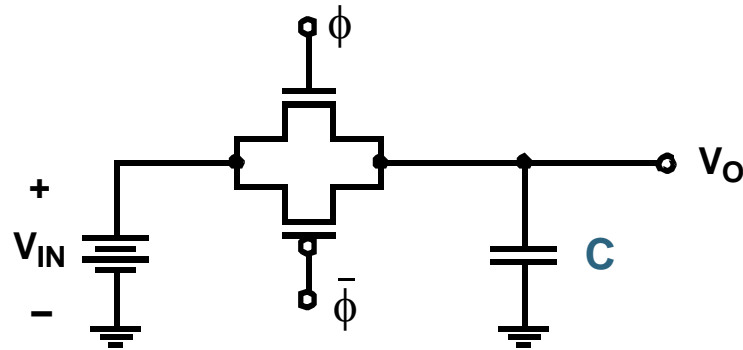
- Assuming fast gating, 50/50 charge split and  $W_n L_n = W_p L_p$

$$\Delta V_o \cong \frac{\frac{1}{2} Q_{chn} + \frac{1}{2} Q_{chp}}{C} = \frac{C_{ox}}{C} \left( V_{IN} - \frac{\phi_H - \phi_L}{2} + \frac{V_{tn} - |V_{tp}|}{2} \right)$$

- Charges fully cancel e.g. for  $V_{IN} = (\phi_H - \phi_L)/2 = V_{DD}/2$ , and  $V_{tn} = |V_{tp}|$ , but there is still signal dependent residual injection

# On Resistance of CMOS Switch

- At least in principle, adding a PMOS can also help with the problem of signal dependent  $R_{on}$  in track mode
  - For increasing  $V_{IN}$ , NMOS resistance goes up, PMOS resistance goes down



$$R \cong \frac{1}{\mu_n C_{ox} \left[ \frac{W}{L} \right]_n (V_{GSn} - V_{tn})} \parallel \frac{1}{\mu_p C_{ox} \left[ \frac{W}{L} \right]_p (|V_{GSp}| - |V_{tp}|)}$$

# Analysis

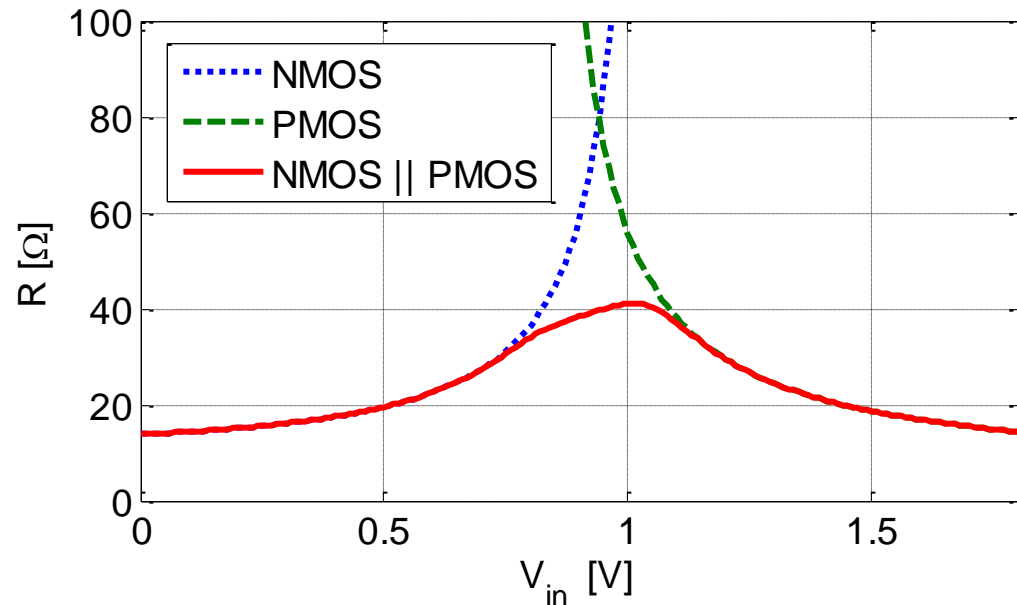
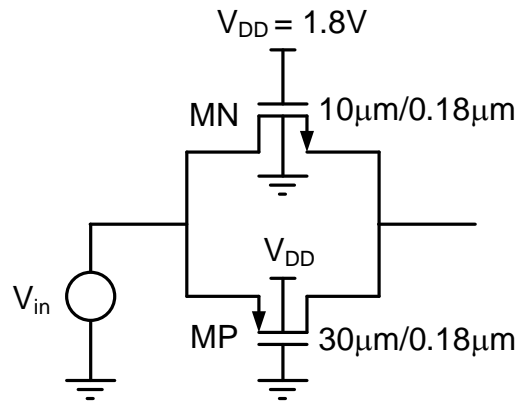
$$R \cong \frac{1}{\mu_n C_{ox} \left[ \frac{W}{L} \right]_n (V_{GSn} - V_{tn})} \parallel \frac{1}{\mu_p C_{ox} \left[ \frac{W}{L} \right]_p (|V_{GSp}| - |V_{tp}|)}$$

$$R \cong \frac{1}{\mu_n C_{ox} \left[ \frac{W}{L} \right]_n (V_{DD} - V_{tn}) - \left( \mu_n C_{ox} \left[ \frac{W}{L} \right]_n - \mu_p C_{ox} \left[ \frac{W}{L} \right]_p \right) v_{in} - \mu_p C_{ox} \left[ \frac{W}{L} \right]_p |V_{tp}|}$$

$$R \cong \frac{1}{\mu_n C_{ox} \left[ \frac{W}{L} \right]_n (V_{DD} - V_{tn} - |V_{tp}|)} \quad \text{if} \quad \mu_n \left[ \frac{W}{L} \right]_n = \mu_p \left[ \frac{W}{L} \right]_p$$

- Independent of  $V_{in} \rightarrow$  too good to be true!
- Missing factors:
  - Backgate effect
  - Short channel effects

# Real CMOS Switch



- Design
  - Size P/N ratio to minimize change in  $R$  over input range
  - Size P and N simultaneously to meet distortion specs
- PMOS brings limited benefit unless the input signal range is large or centered near  $V_{DD}/2$

**EE 240C**

**Analog-Digital Interface Integrated Circuits**

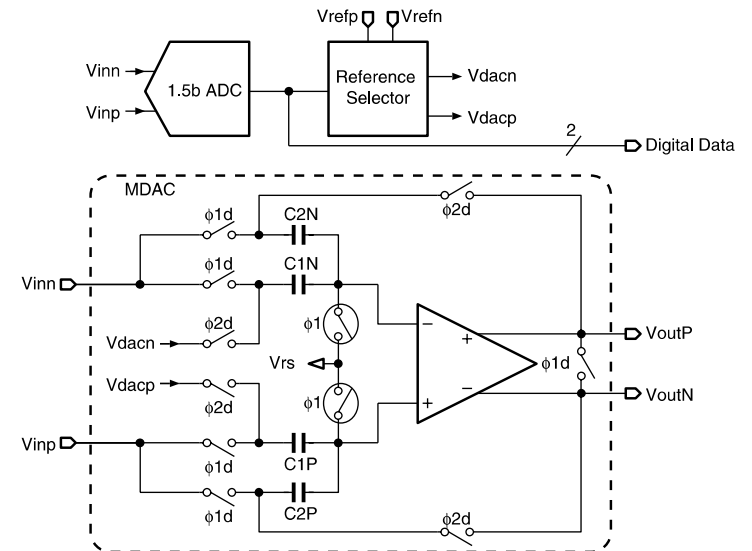
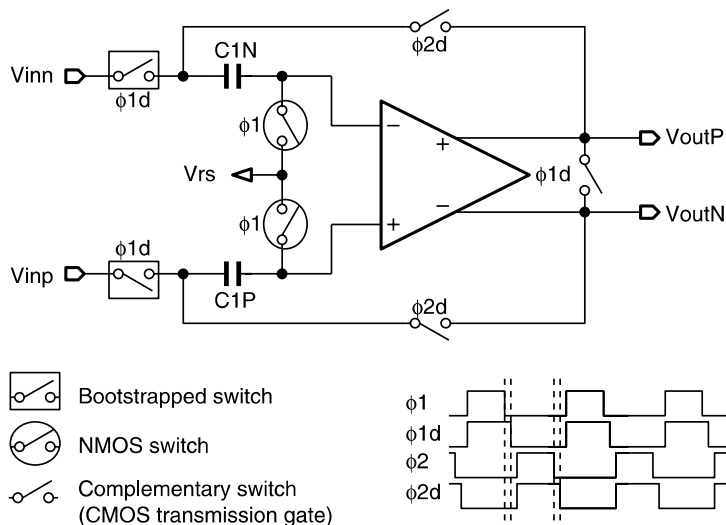
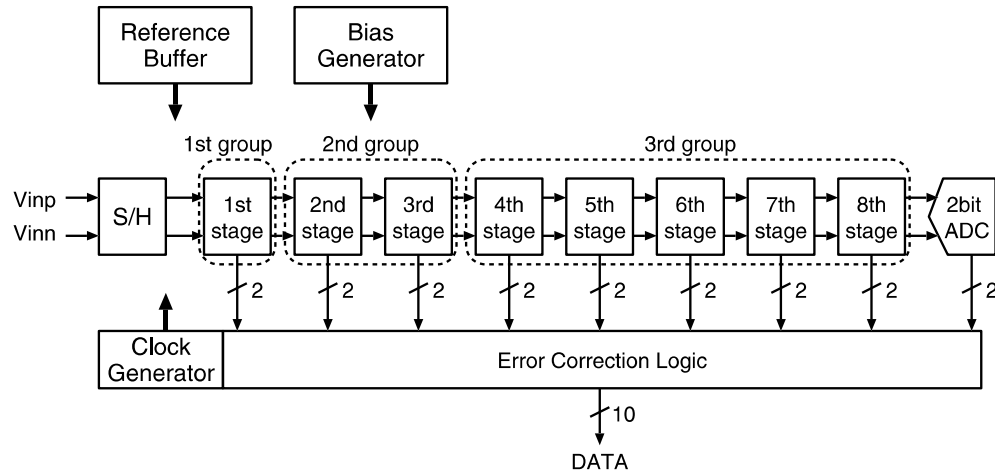
**Track & Hold Amplifier – Bootstrapping**

# Outline

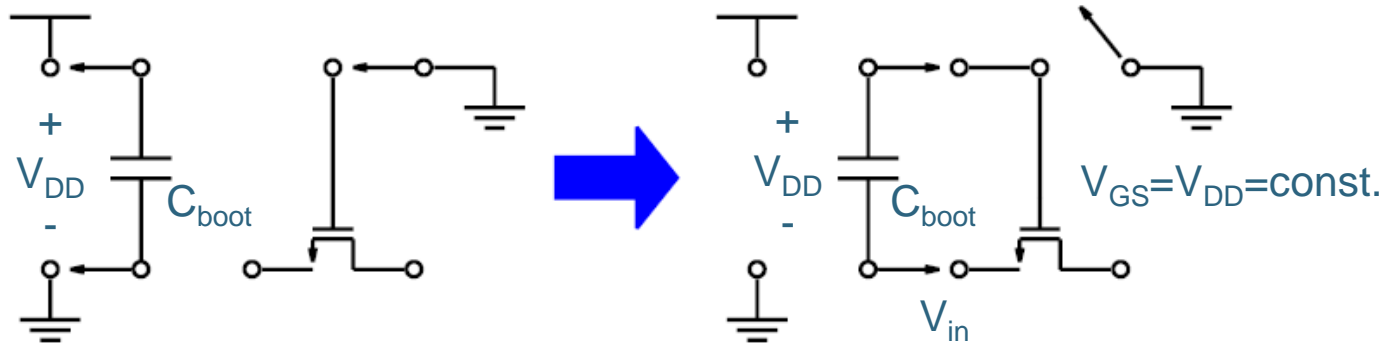
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- Elementary track-and-hold circuit and its nonidealities
- First order improvements to elementary track-and-hold
- Advanced techniques
  - Clock bootstrapping
  - Bottom plate sampling
- Settling and noise analysis in charge-redistribution track-and-hold circuit
- Noise simulation example

# SHA / Pipelined Stage Example



# Clock Bootstrapping

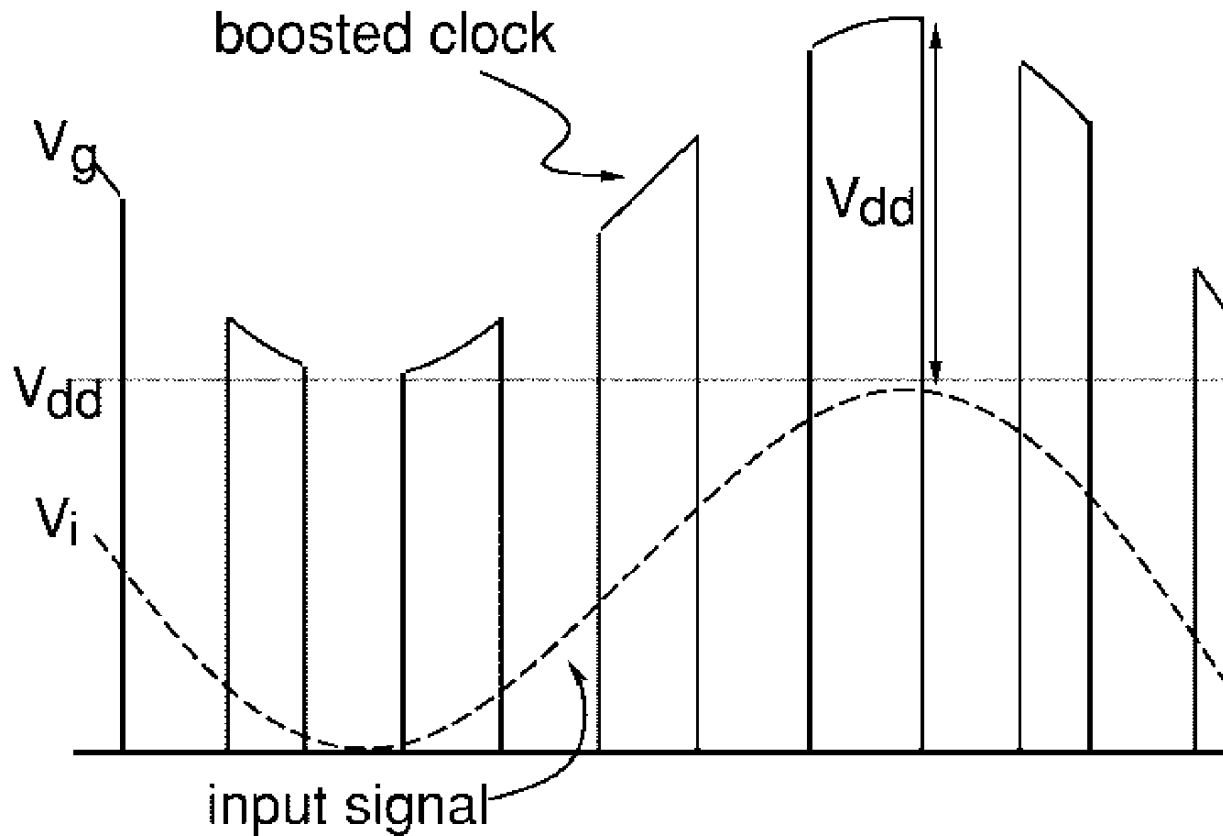


A. Abo, "Design for Reliability of Low-voltage, Switched-capacitor Circuits," PhD Thesis, UC Berkeley, 1999.

- Phase 1
  - $C_{boot}$  is precharged to  $V_{DD}$
  - Sampling switch is off
- Phase 2
  - Sampling switch is on with  $V_{GS} = V_{DD} = \text{const.}$
  - To first order, both  $R_{on}$  and channel charge are signal independent



# Waveforms



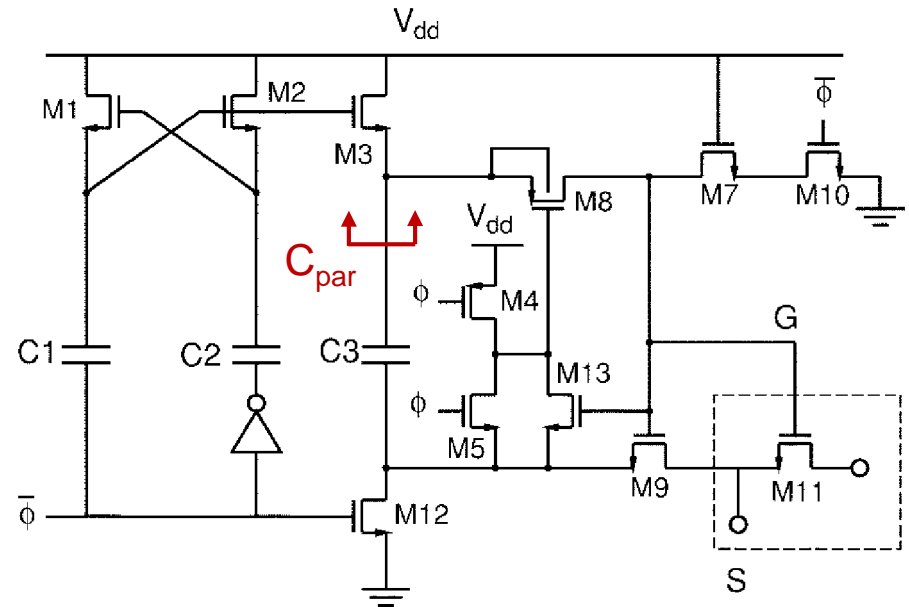
A. Abo, "Design for Reliability of Low-voltage, Switched-capacitor Circuits," PhD Thesis, UC Berkeley, 1999.

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# Limitations

- Efficacy of bootstrap circuit is reduced by
  - Backgate effect
  - Parasitic capacitance  $C_{\text{par}}$  at top plate of  $C_3 = C_{\text{boot}}$
- Charge conservation:
 
$$C_{\text{boot}} V_{DD} = C_{\text{boot}} V_{\text{GS,switch}} + C_{\text{par}} (V_{\text{GS,switch}} + V_{\text{in}})$$



$$R \cong \frac{1}{\mu_n C_{ox} \left[ \frac{W}{L} \right]_n \left( \frac{C_{\text{boot}}}{C_{\text{boot}} + C_{\text{par}}} V_{DD} - \frac{C_{\text{par}}}{C_{\text{boot}} + C_{\text{par}}} V_{\text{in}} - \underbrace{V_{tn}[V_{\text{in}}]}_{\text{Backgate effect}} \right)}$$

# Alternative Implementation

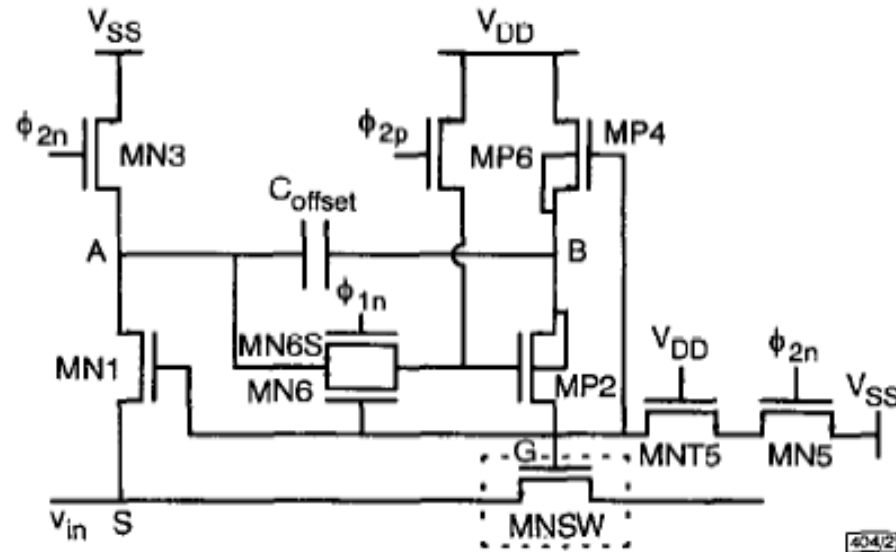


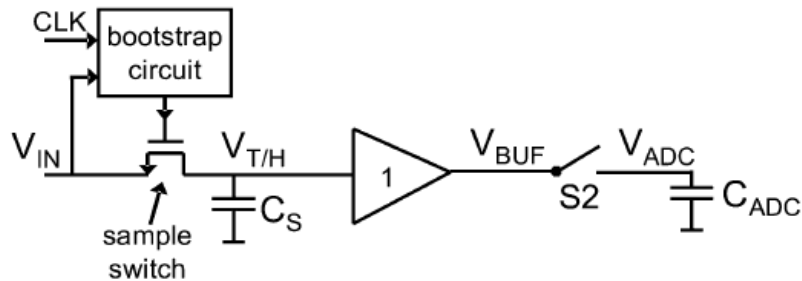
Fig. 2 Proposed implementation

Dessouky and Kaiser, "Input switch configuration suitable for rail-to-rail operation of switched opamp circuits," Electronics Letters, Jan. 1999.

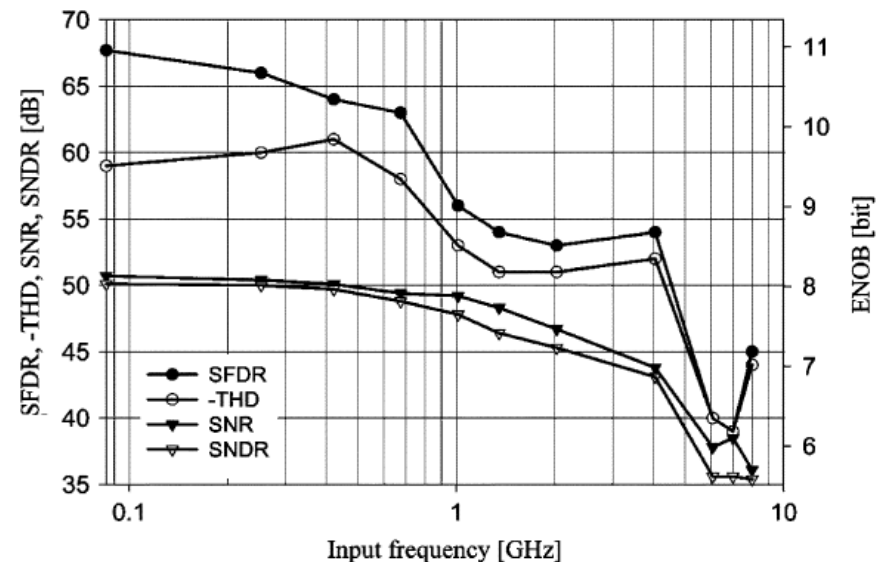
- Less complex, but  $C_{par}$  tends to be larger due to two parasitic well capacitances

# Performance of Bootstrapped Samplers

- Bootstrapped “top plate” sampling works well up to ~10bit resolution
- Use “bottom plate sampling” for higher resolution (see later)
- Example



[Louwsma, JSSC 4/2008]



# **EE 240C**

## **Analog-Digital Interface Integrated Circuits**

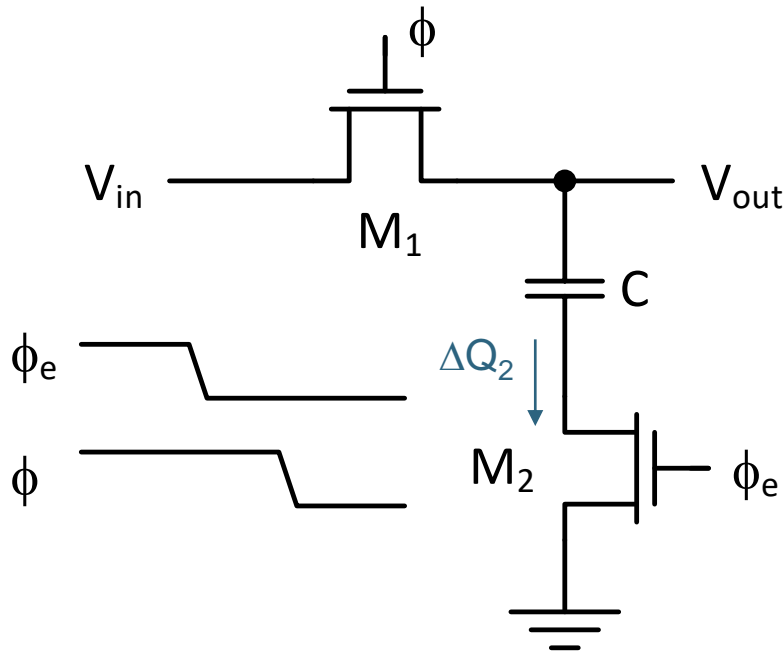
### **Track & Hold Amp – Bottom Plate Sampling**

# Bottom Plate Sampling

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- What if we want to do much better, e.g. 16 bits?
- Basic idea
  - Make “switched” voltage ( $V_{in}$ ?) constant ...
  - How? Sample signal at the “grounded” side of the capacitor to achieve signal independent sampling
- References
  - D. J. Allstot and W. C. Black, Jr., “Technological Design Considerations for Monolithic MOS Switched–Capacitor Filtering Systems,” Proc. IEEE, pp. 967–986, Aug. 1983.
  - K.–L. Lee and R. G. Meyer, “Low–Distortion Switched–Capacitor Filter Design Techniques,” IEEE J. Solid–State Circuits, pp. 1103–1113, Dec. 1985.
- First look at single ended half circuit for simplicity

# Bottom Plate Sampling Analysis (1)



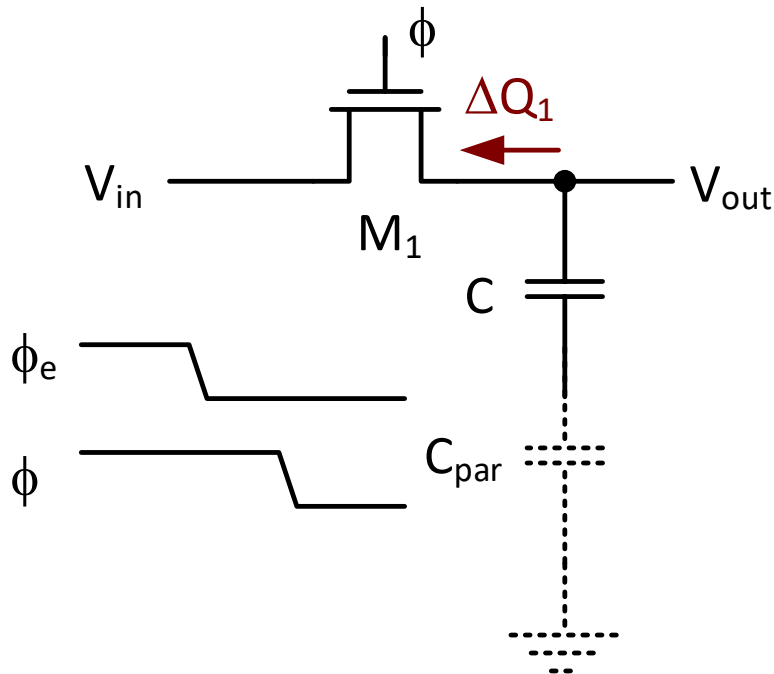
- Turn  $M_2$  off "slightly" before  $M_1$ 
  - Typically few hundred ps delay between falling edges of  $\phi_e$  and  $\phi$
- During turn off,  $M_2$  injects charge
$$\Delta Q_2 \cong \frac{1}{2} W L C_{ox} (\phi_H - V_{tn})$$
- To first order, the charge injected by  $M_2$  is signal independent

- Voltage across  $C$

$$V_C = V_{in} + \frac{\Delta Q_2}{C}$$



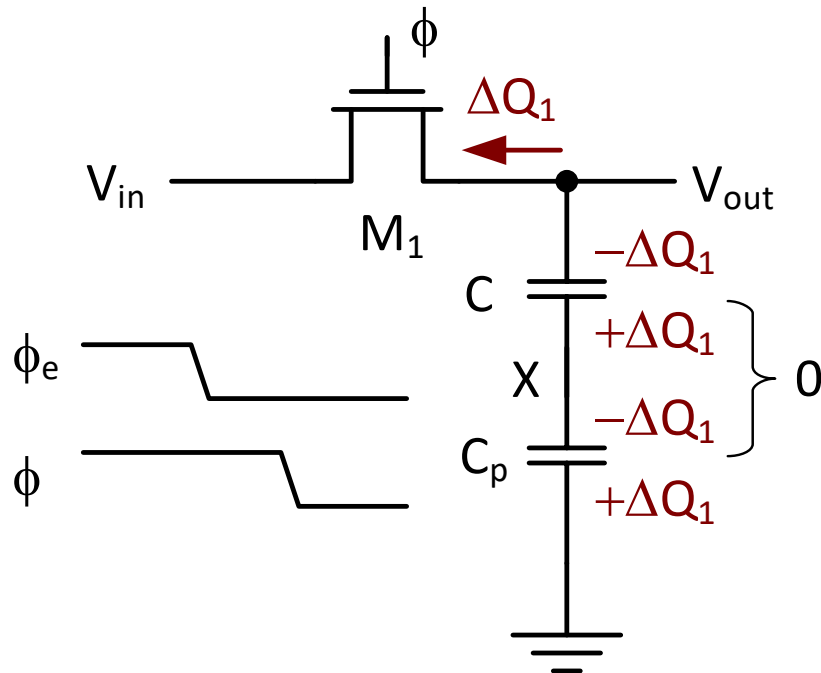
# Bottom Plate Sampling Analysis (2)



$$\Delta Q_1 \cong \frac{1}{2} W L C_{ox} (\phi_H - V_{in} - V_{tn})$$

- Next, turn off M1
- M1 will inject signal dependent charge onto the series combination of C and the parasitic capacitance at its bottom plate ( $C_{par}$ )
- Looks like, this is not much different from the conventional top-plate sampling?
  - But wait...

# Bottom Plate Sampling Analysis (3)

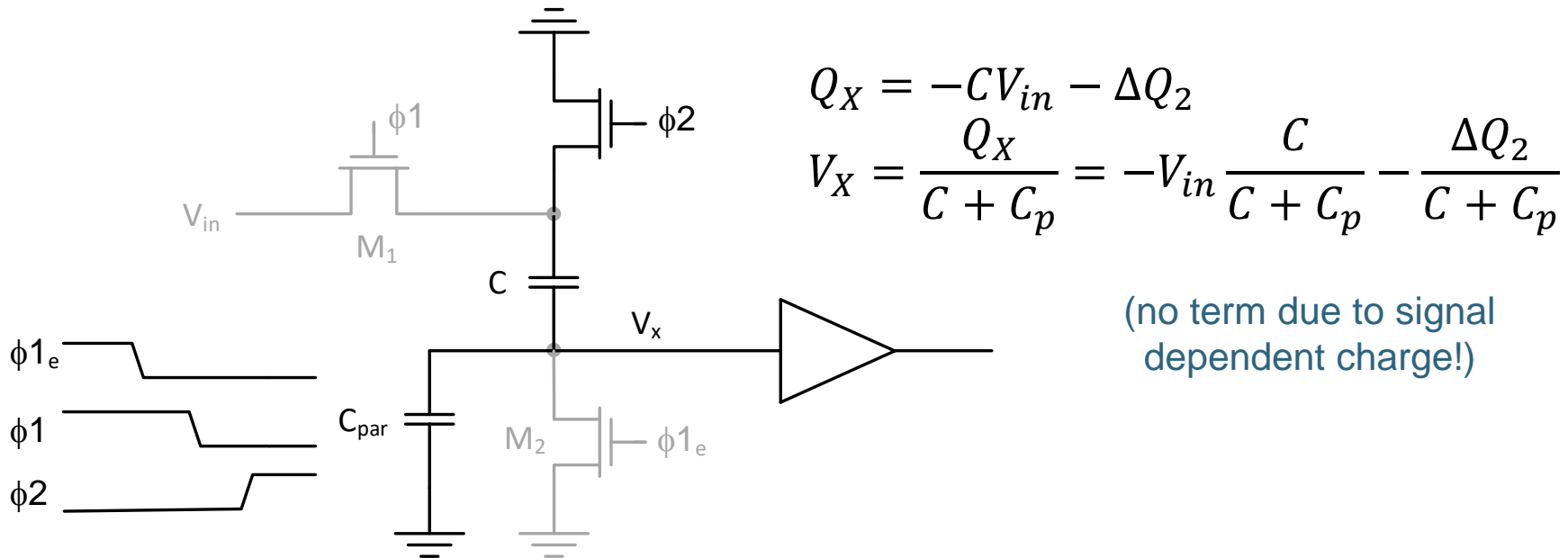


$$Q_X = -CV_{in} - \underbrace{\Delta Q_2}$$

Charge injected by M2  
(Signal independent)

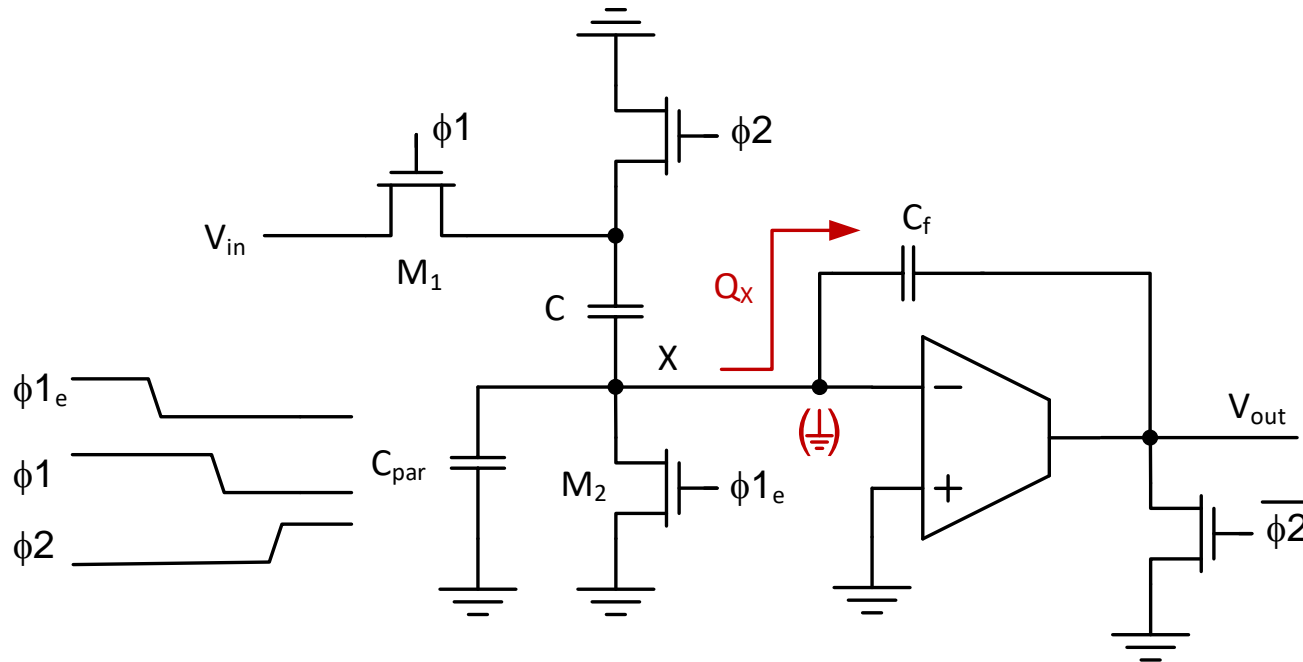
- Interesting observation
  - Even though M1 injects some charge, the total charge at node X cannot change!
- Idea
  - Process total charge at node X instead of voltage across C
- The charge can be processed in two ways
  - Open-loop
  - Closed-loop (charge redistribution)

# Open-Loop Charge Processing



- Remaining drawback
  - $C_{par}$  (and buffer input capacitance) is usually weakly nonlinear and will introduce some harmonic distortion

# Closed-Loop Charge Processing



- Amplifier forces voltage at node  $X$  to “zero”
  - Means that charge at node  $X$  must redistribute onto feedback capacitor  $C_f$

# Charge Conservation Analysis

Charge at node X during  $\phi 1$ :  $Q_{X1} = -CV_{in} - \Delta Q_2 + 0 \cdot C_f$

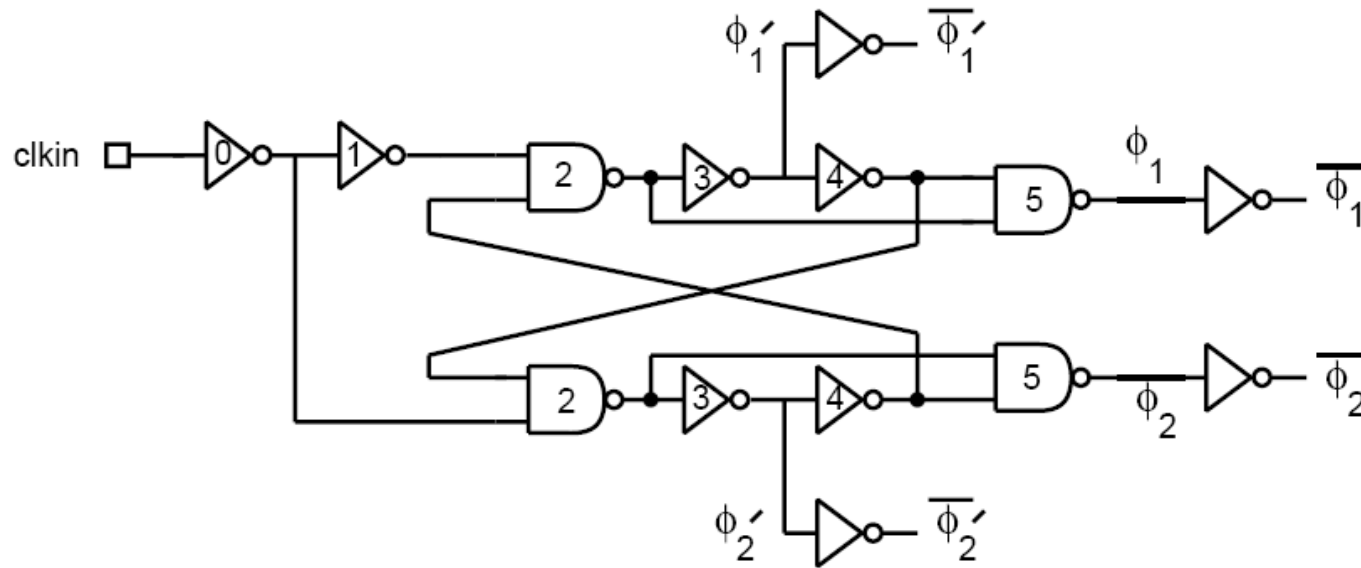
Charge at node X during  $\phi 2$ :  $Q_{X2} = -C_f V_{out}$

Charge Conservation: 
$$\begin{aligned} Q_{X1} &= Q_{X2} \\ -CV_{in} - \Delta Q_2 &= -C_f V_{out} \end{aligned}$$

$$\therefore V_{out} = \frac{C}{C_f} V_{in} + \frac{\Delta Q_2}{C_f}$$

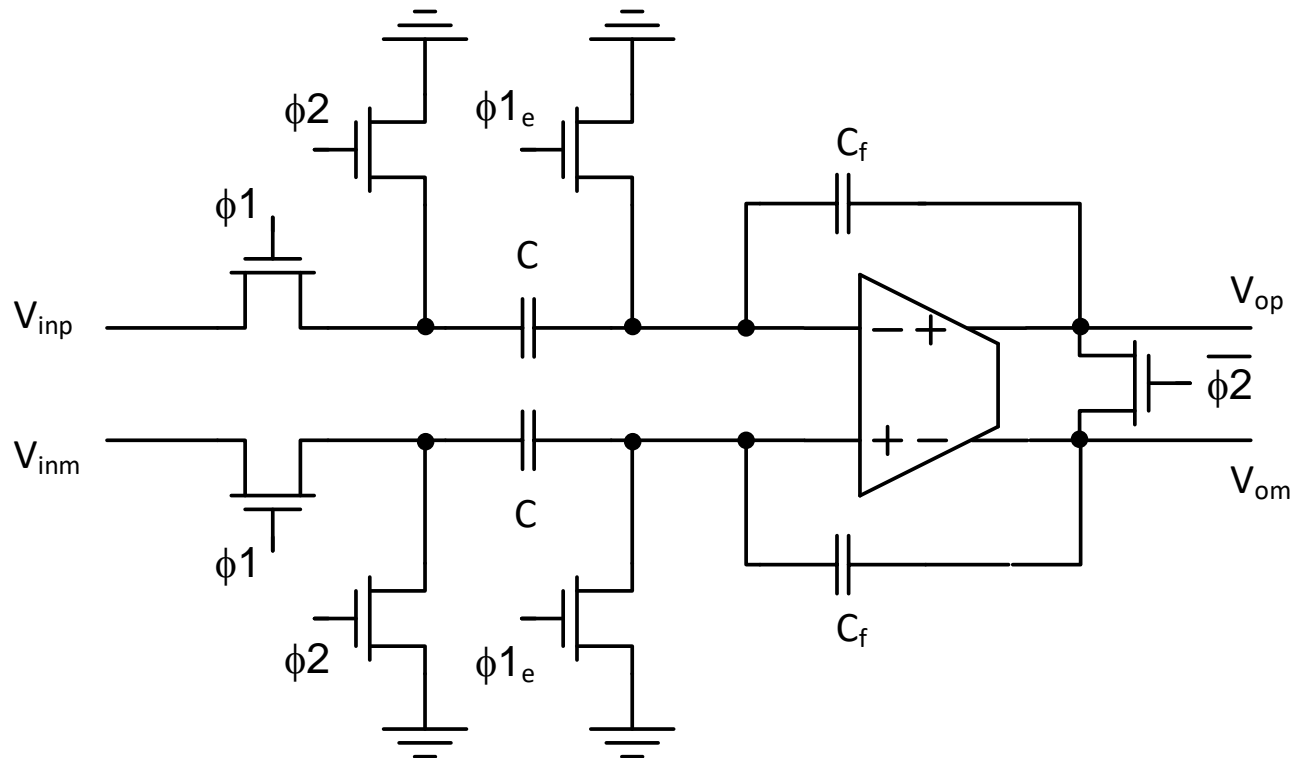
- No gain error
- Offset term due to signal independent injection from M2 can be easily removed using a differential architecture

# Clock Generation



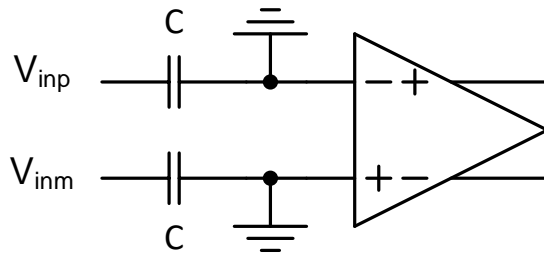
[A. Abo, "Design for Reliability of Low-voltage, Switched-capacitor Circuits," PhD Thesis, UC Berkeley, 1999]

# Fully Differential Circuit



# Analysis (1)

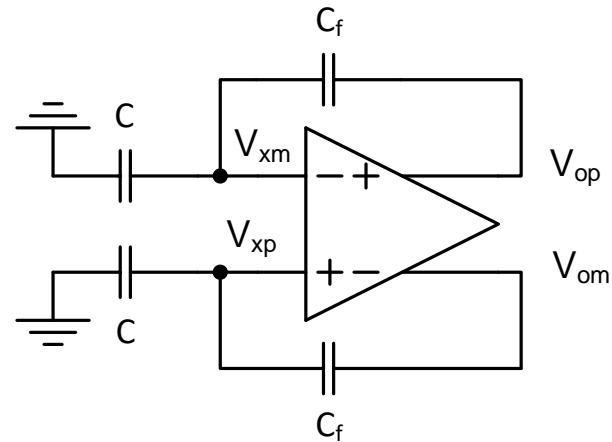
During  $\phi 1$



$$Q_{1m} = -CV_{inp} + \Delta Q$$

$$Q_{1p} = -CV_{inm} + \Delta Q$$

During  $\phi 2$



$$Q_{2m} = CV_{xm} - C_f(V_{op} - V_{xm})$$

$$Q_{2p} = CV_{xp} - C_f(V_{om} - V_{xp})$$

$$\begin{aligned} 1) \quad Q_{1m} &= Q_{2m} & V_{xm} &= V_{xp} & \frac{V_{op} + V_{om}}{2} &= V_{oc} \\ 2) \quad Q_{1p} &= Q_{2p} \end{aligned}$$



# Analysis (2)

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- Subtracting 1) and 2) yields

$$V_{op} - V_{om} = \frac{C}{C_f} (V_{inp} - V_{inm})$$

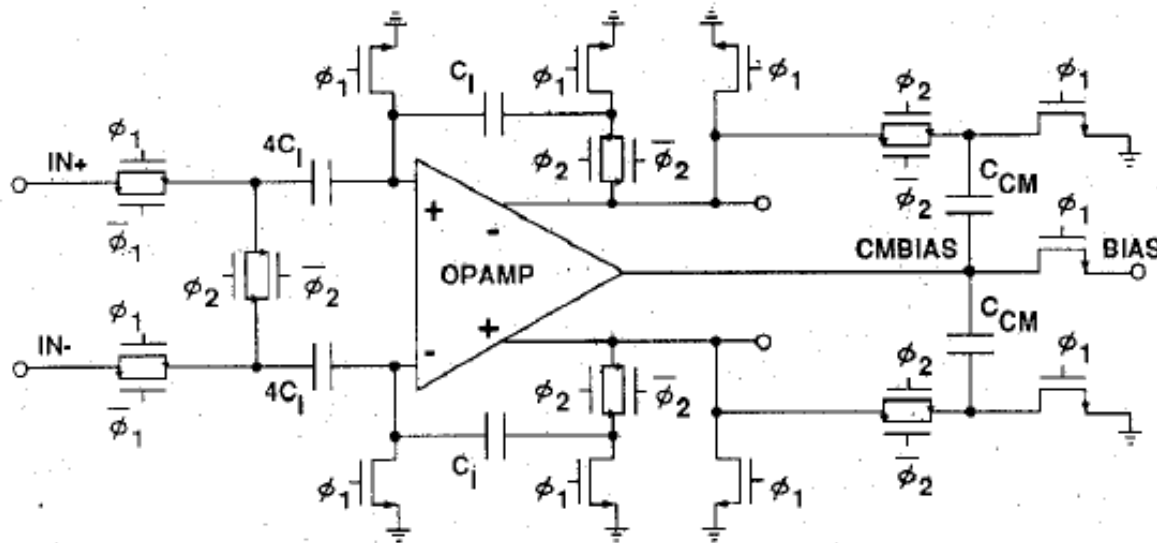
- Adding 1) and 2) yields

$$-C(V_{inp} + V_{inm}) + 2\Delta Q = (C + C_f)(V_{xp} + V_{xm}) - C_f(V_{op} + V_{om})$$

$$V_{xc} = \frac{\Delta Q}{C + C_f} + \frac{C_f}{C + C_f} V_{oc} - \frac{C}{C + C_f} V_{ic}$$

- Variations in  $V_{ic}$  show up as common mode variations at the amplifier input
  - Need amplifier with good CMRR

# T/H with Common Mode Cancellation

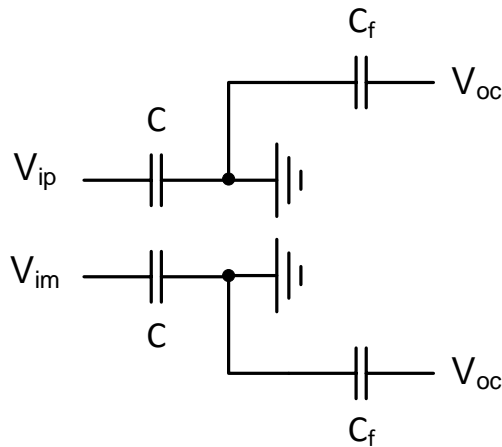


S.H. Lewis & P.R. Gray, "A Pipelined 5 MSample/s 9-bit Analog-to-Digital Converter", IEEE J. Solid-State Circuits, pp. 954-961, Dec. 1987

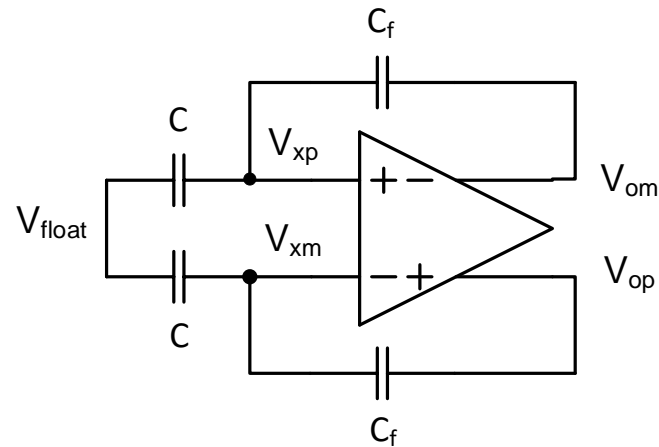
- Shorting switch allows to re-distribute only differential charge on sampling capacitors
- Common mode at OPAMP input becomes independent of common mode at circuit input terminals (IN+ /IN-)
- Original idea: Yen & Gray, JSSC 12/1982

# Analysis (1)

During  $\phi 1$



During  $\phi 2$



- Charge conservation at  $V_{ip}, V_{im}$  and  $V_{float}$

$$(V_{ip} + V_{im}) \cdot C = (V_{float} - V_{xp}) \cdot C + (V_{float} - V_{xm}) \cdot C$$

$$V_{ic} = V_{float} - V_{xc}$$

$$V_{float} = V_{ic} + V_{xc}$$

## Analysis (2)

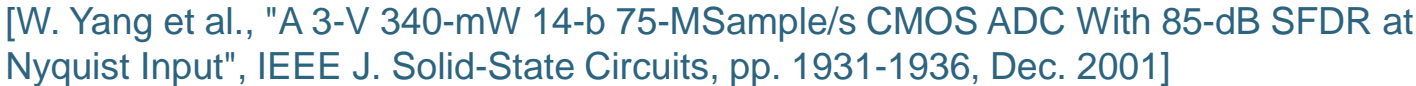
---

- Common mode charge conservation at amplifier inputs

$$\begin{aligned}-V_{ic} \cdot C - V_{oc} \cdot C_f &= -(V_{float} - V_{xc}) \cdot C - (V_{oc} - V_{xc}) \cdot C_f \\ -V_{ic} \cdot C &= -([V_{ic} + V_{xc}] - V_{xc}) \cdot C + V_{xc} \cdot C_f \\ 0 &= V_{xc}\end{aligned}$$

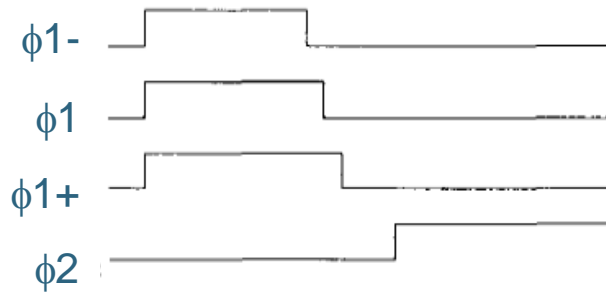
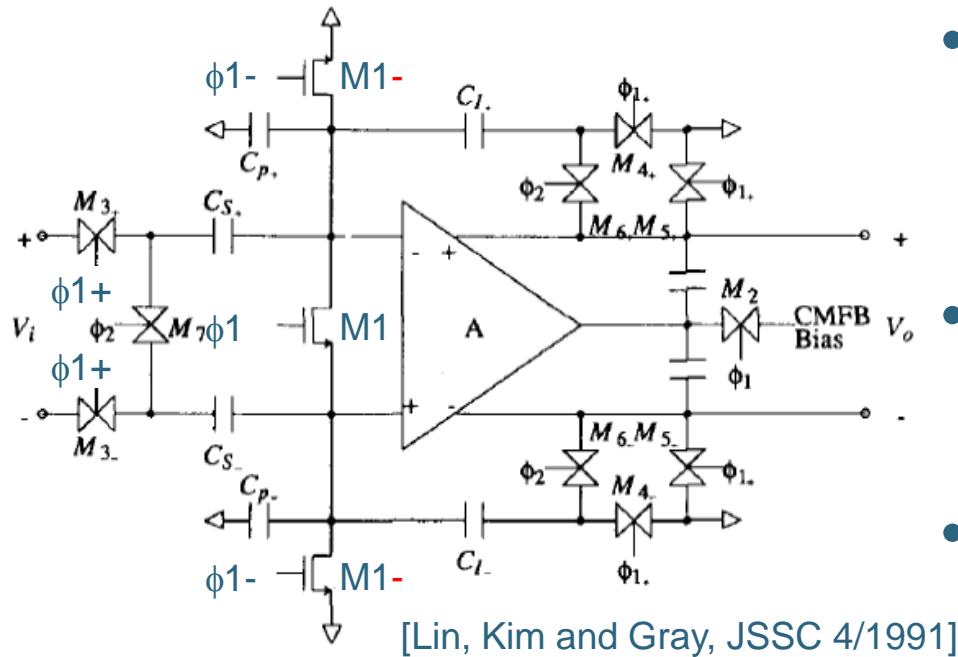
- Amplifier input common mode ( $V_{xc}$ ) is independent of
  - Input common mode ( $V_{ic}$ )
  - Output common mode ( $V_{oc}$ )

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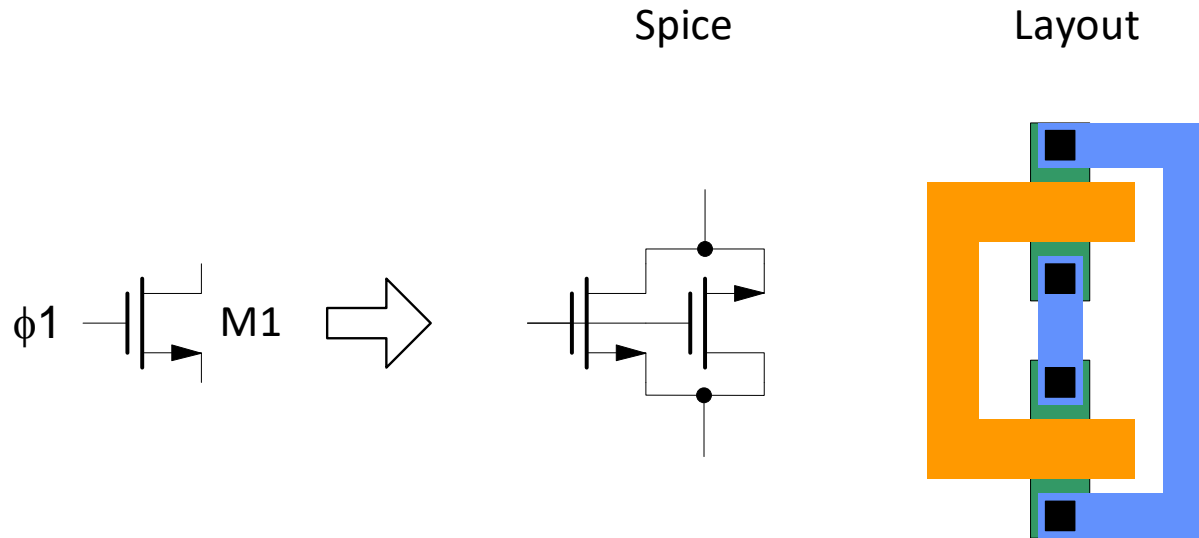
- Johan Vanderhaegen  
2019 Fall

# Sampling Network Design Considerations



- M1- switches only needed to set common mode; M1 is actual sampling switch
  - Make M1 larger than M1-
- Ideally turn off M1- before M1
  - In practice, usually OK to turn off simultaneously
- In track mode, the total path resistance is  $R(M_3)$  plus bottom plate switch resistance
  - Since  $R(M_3)$  is signal dependent, make its resistance small compared to that of bottom plate network

# Schematic Entry and Layout of M1



- Use antiparallel devices to implement M1
  - Needed in simulation to guarantee circuit symmetry
    - E.g. BSIM model is not necessarily perfectly symmetric with respect to drain/source!
  - Needed in layout to ensure symmetry in presence of drain/source asymmetry due to processing artifacts

# What Ultimately Limits Linearity?

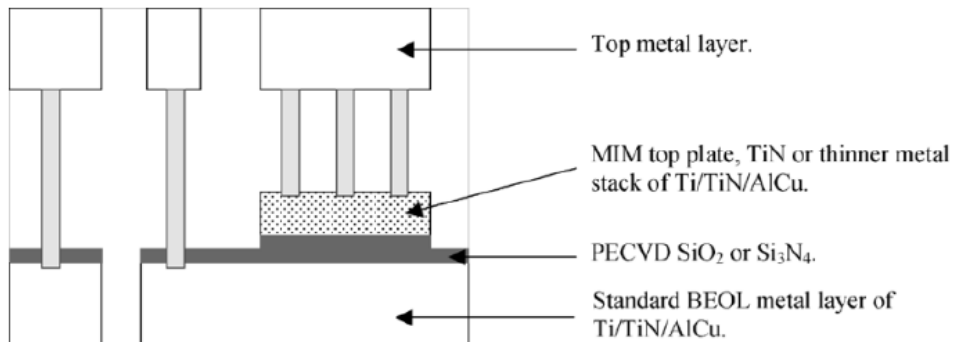
---

- Track mode nonlinearity due to  $R=f(V_{in})$ 
  - Mitigate using clock bootstrapping and proper partitioning of total path resistance
  - Eventually, bootstrapping falls apart at high frequencies, due to parasitic capacitances inside the bootstrap circuit
- Mismatch in half-circuit charge injection due to  $R=f(V_{in})$ 
  - Bottom plate switches in the two half circuits see input dependent impedance; this creates input dependent charge injection mismatch
  - Bootstrapping helps; ultimately limited by backgate effect
  - This effect is often fairly independent of frequency (somewhat dependent on realization of top plate switch)
- In high performance designs, can achieve ~80–100dB linearity up to a few hundreds of MHz



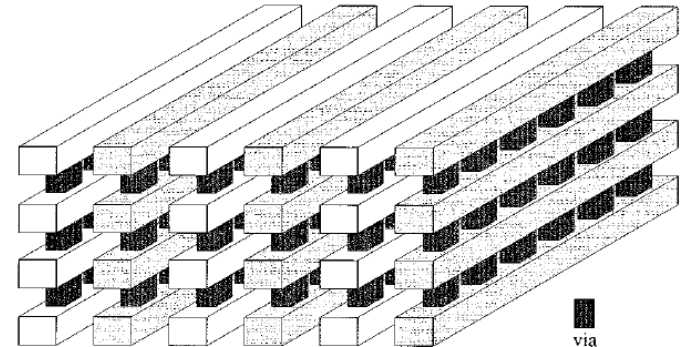
# Capacitors

## Metal-Insulator-Metal (MIM)



[Ng, Trans. Electron Dev., 7/2005]

## Vertical Parallel Plate (VPP)

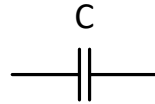


[Aparicio, JSSC 3/2002]

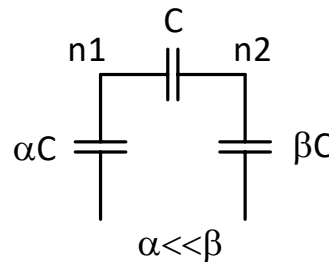
- Typically 1–2 fF/mm<sup>2</sup> (10–20 fF/mm<sup>2</sup> for advanced structures)
  - For 1 fF/mm<sup>2</sup>, a 10 pF capacitor occupies ~100mm x 100mm
- Both MIM and VPP capacitors have good electrical properties
  - Mostly worry about parasitic caps
  - Series and parallel resistances are often not a concern

# Plate Parasitics

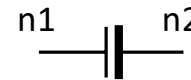
Ideal Capacitor



Typical Integrated  
Circuit Capacitor

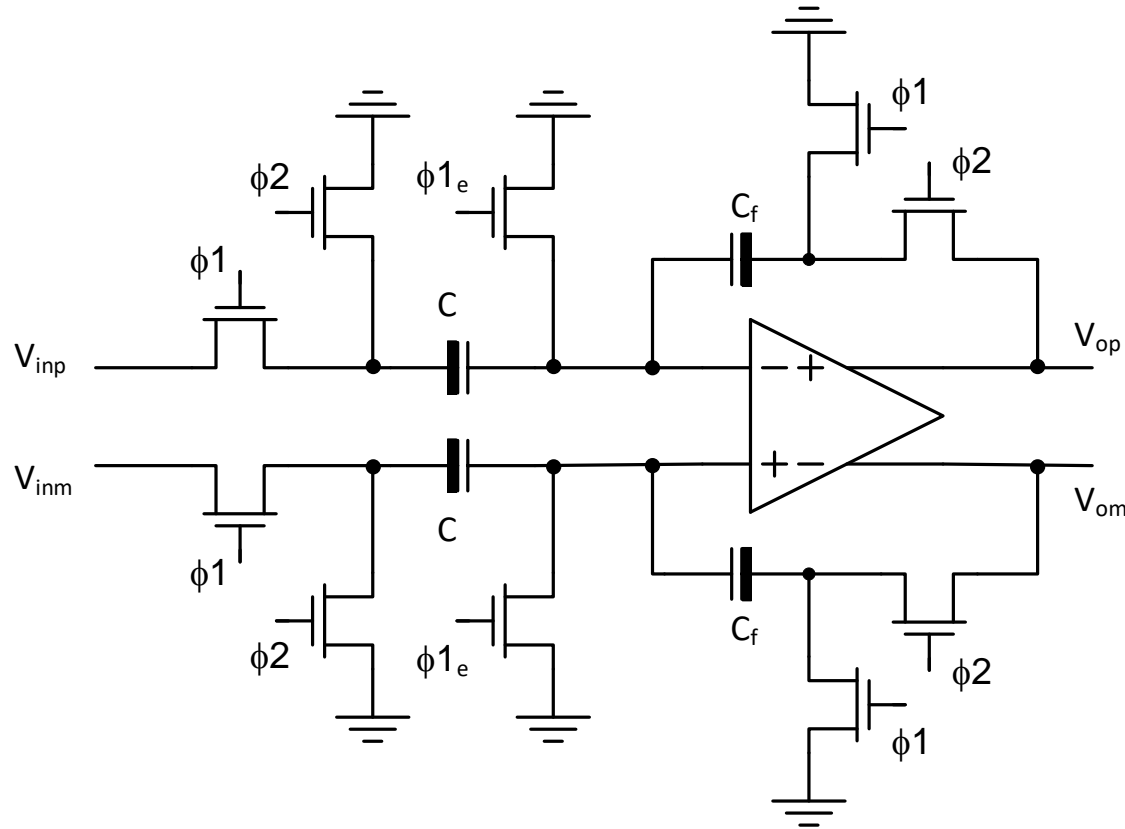


Symbol



- Node n1 is usually the "physical" top plate of the capacitor
  - Makes nomenclature very confusing, since this plate is typically used as the "electrical" bottom plate in a sampling circuit (in the context of "bottom plate sampling")
- Typical values for a MIM capacitor
  - $a=1\%$ ,  $b=10\%$

# Proper Connection of Capacitors



- “Fat plate” is oriented away from virtual ground nodes to avoid reduction of feedback factor and reduce noise gain and interference

# **EE 240C**

## **Analog-Digital Interface Integrated Circuits**

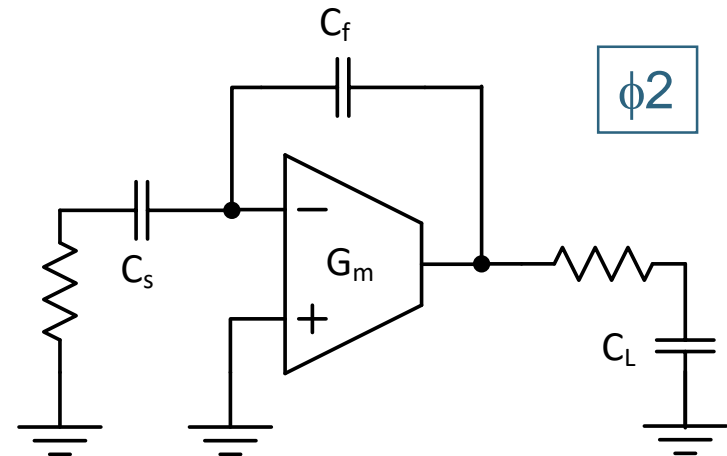
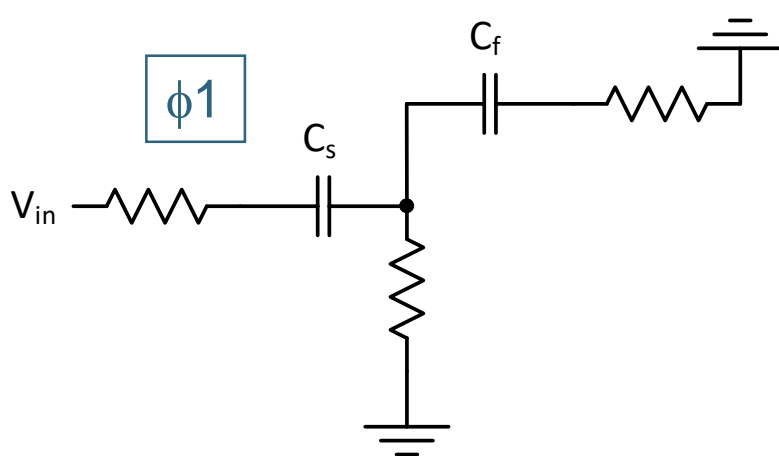
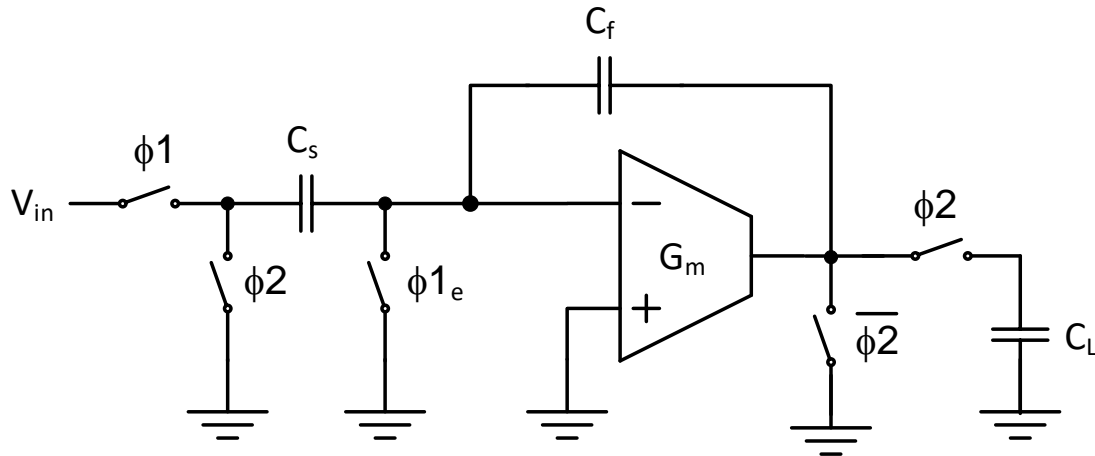
### **Track & Hold Amp – Settling**

# Outline

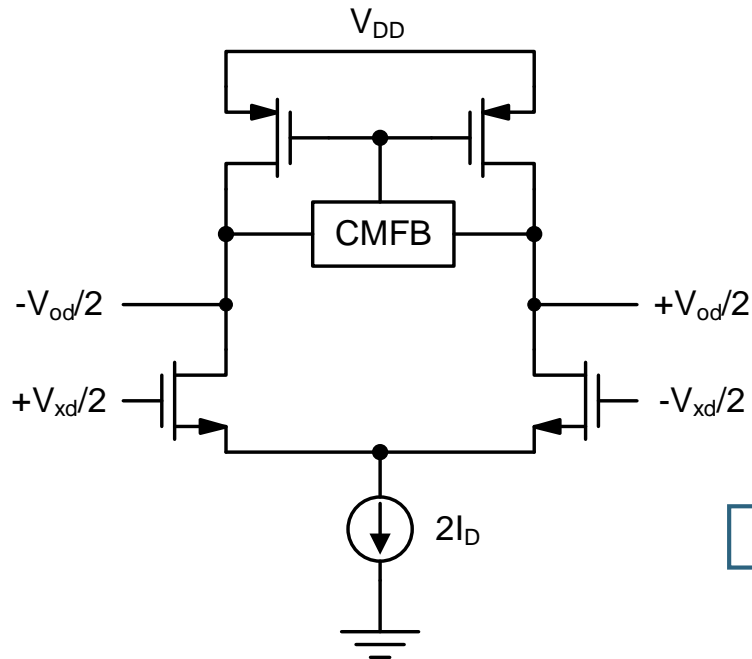
---

- Elementary track-and-hold circuit and its nonidealities
- First order improvements to elementary track-and-hold
- Advanced techniques
  - Clock bootstrapping
  - Bottom plate sampling
- Settling and noise analysis in charge-redistribution track-and-hold circuit
- Noise simulation example

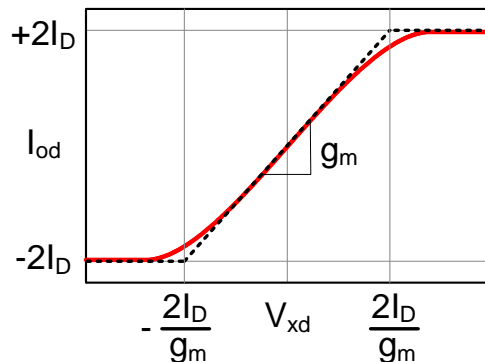
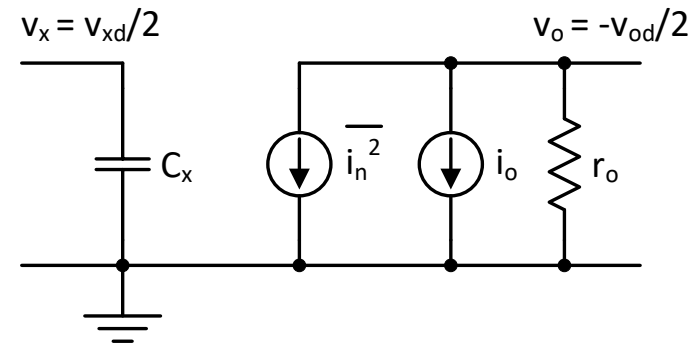
# Settling and Noise Analysis



# First Order Amplifier Model

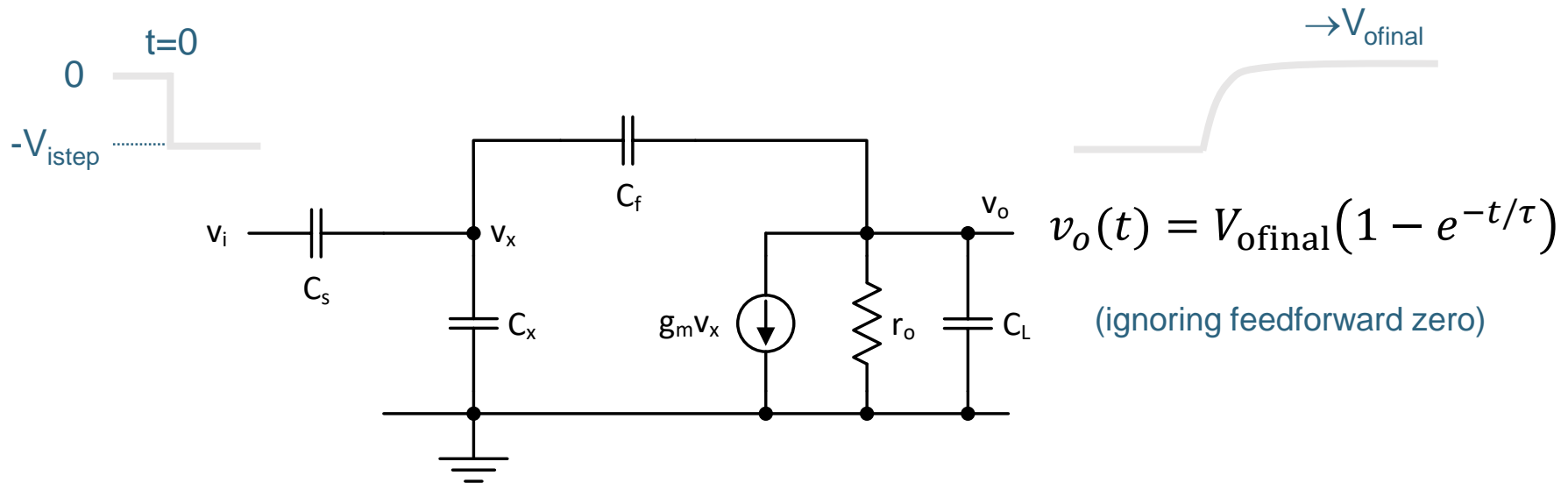


Piecewise linear half-circuit



$$i_o = \begin{cases} g_m v_x & \text{for } |g_m v_x| < I_D \\ I_D \cdot \text{sign}(v_x) & \text{else} \end{cases}$$

# Linear Settling (Small Input Step)

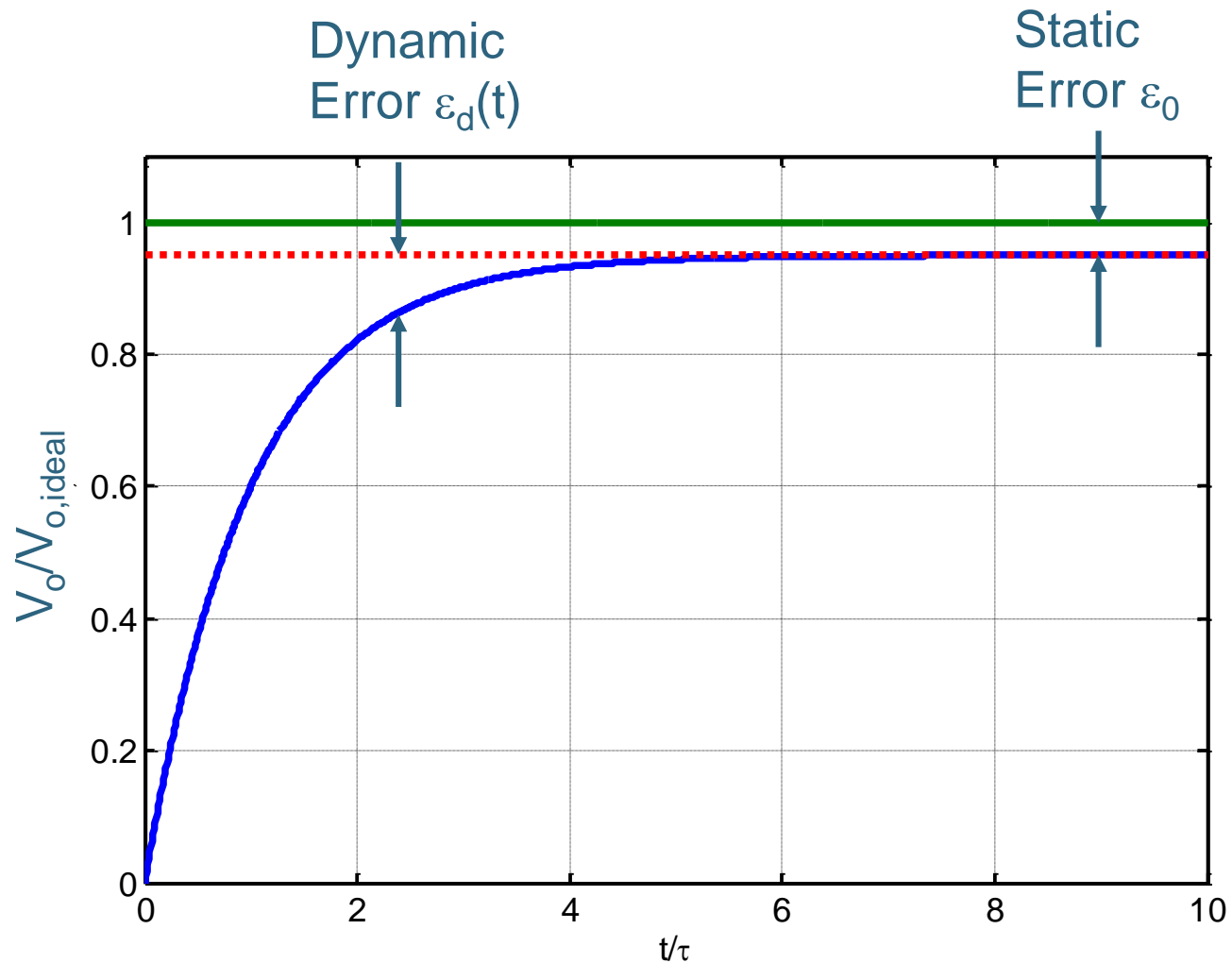


- Important parameter: Return factor or "feedback factor"  $\beta$

$$\beta = \frac{C_f}{C_f + C_s + C_x}$$



# Waveform Detail



# Static Settling Error

- Ideal output voltage for  $t \rightarrow \infty$   $V_{\text{ofinal,ideal}} = V_{\text{istep}} \cdot \frac{C_s}{C_f}$

- Actual output voltage (from detailed analysis)

$$V_{\text{ofinal}} = V_{\text{istep}} \cdot \frac{C_s}{C_f} \cdot \frac{T_0}{1 + T_0} \quad T_0 = \beta \cdot g_m r_o = \beta \cdot a_{vo}$$

- Define static settling error

$$\varepsilon_0 = \frac{V_{\text{ofinal}} - V_{\text{ofinal,ideal}}}{V_{\text{ofinal,ideal}}} = \frac{\frac{T_0}{1 + T_0} - 1}{1} = -\frac{1}{1 + T_0} \cong -\frac{1}{T_0}$$

- Example:  $T_0 = 1000 \rightarrow 0.1\%$  static settling error

# Dynamic Settling Error

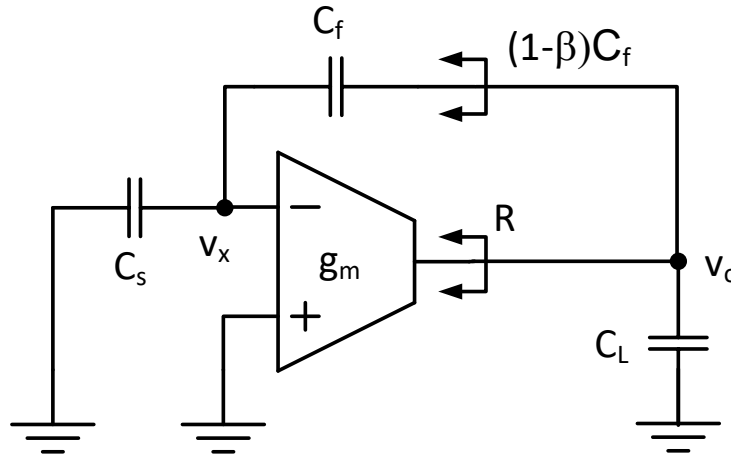
$$\varepsilon_{\text{dynamic}}(t) = \frac{v_o(t) - V_{\text{ofinal}}}{V_{\text{ofinal}}} = \frac{V_{\text{ofinal}}(1 - e^{-t/\tau}) - V_{\text{ofinal}}}{V_{\text{ofinal}}} = -e^{-t/\tau}$$

$$N = \frac{t_s}{\tau} = -\ln(\varepsilon_d)$$

$\varepsilon_{\text{dynamic}}$	N
1%	4.6
0.1%	6.9
0.01%	9.2

# Time Constant

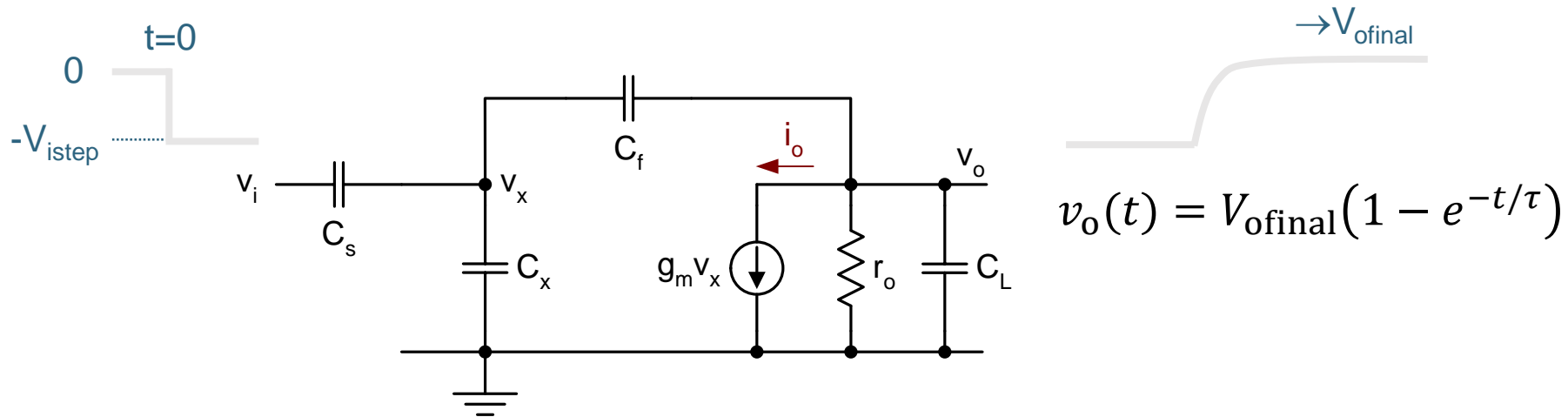
$$\beta = \frac{C_f}{C_f + C_s + C_x}$$



$$R = \frac{1}{\beta g_m} \quad C_{L\text{tot}} = C_L + (1 - \beta)C_f$$

$$\tau = \frac{1}{\beta} \cdot \frac{C_{L\text{tot}}}{g_m}$$

# Transconductor Current



- During linear settling, the current delivered by the transconductor is

$$i_o \cong -C_{Ltot} \frac{dv_o(t)}{dt} = -C_{Ltot} \frac{V_{ofinal}}{\tau} e^{-t/\tau}$$

- Peak current occurs at  $t=0$

$$|i_o|_{max} = C_{Ltot} \frac{V_{ofinal}}{\tau}$$

# Slewing

- The amplifier can deliver a maximum current of  $I_D$

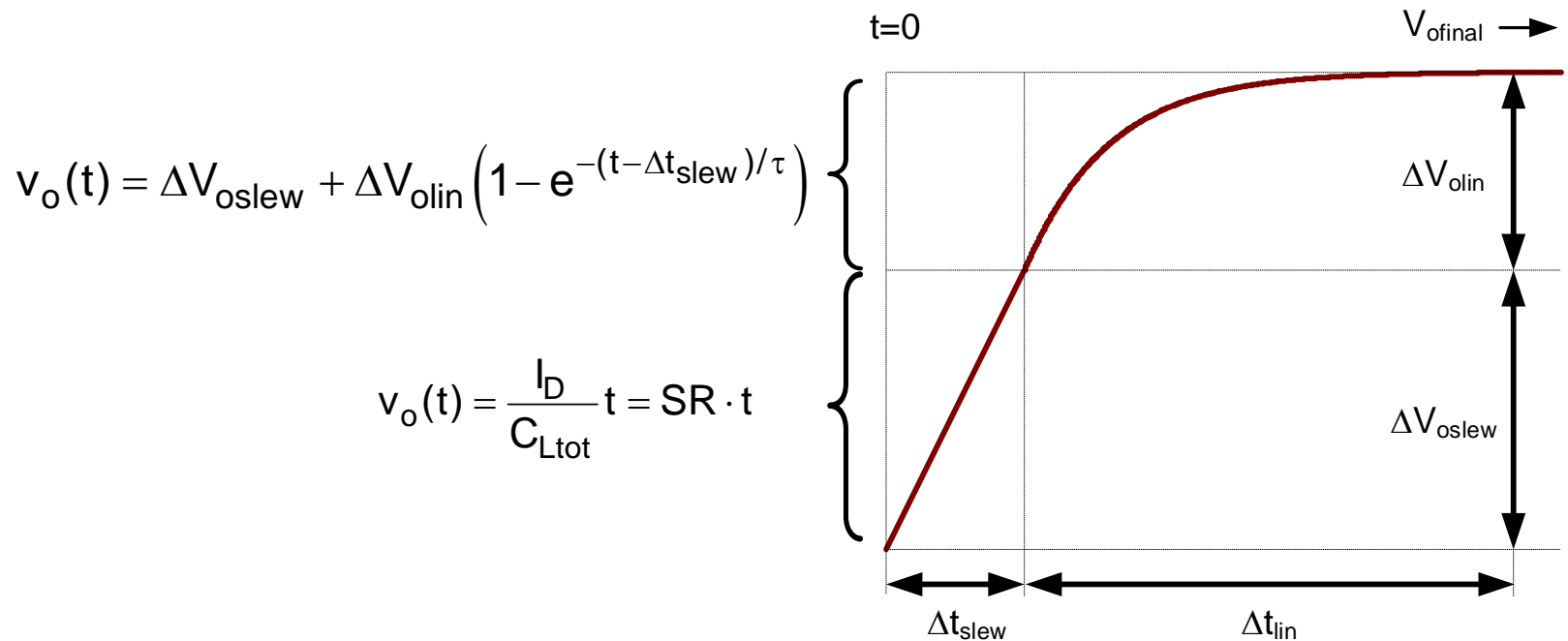
- If  $|i_o|_{\max} > I_D$ , slewing occurs

$$|i_o|_{\max} = C_{L\text{tot}} \frac{V_{\text{ofinal}}}{\tau} > I_D$$

$$C_{L\text{eff}} \frac{V_{\text{ofinal}}}{\frac{1}{\beta} \cdot \frac{C_{L\text{tot}}}{g_m}} > I_D \quad \Rightarrow \quad \frac{g_m}{I_D} > \frac{1}{\beta V_{\text{ofinal}}} \quad \text{or} \quad V^* < 2\beta V_{\text{ofinal}}$$

- Example:  $\beta=0.5$ ,  $V_{\text{ofinal}}=0.5\text{V} \rightarrow g_m/I_D > 4 \text{ S/A}$  ( $V^* < 500\text{mV}$ ) will result in slewing
- Challenging to avoid slewing, unless
  - Bias at very low  $g_m/I_D$  (power inefficient & large headroom)
  - Feedback factor is small (large closed-loop gain,  $C_s/C_f$ )
  - Output voltage swing is small

# Output Waveform with Initial Slewing



- Continuous derivative in the transition slewing  $\rightarrow$  linear requires

$$\frac{I_D}{C_{L\text{tot}}} = \frac{\Delta V_{\text{olin}}}{\tau} \quad \Delta V_{\text{olin}} = \frac{\tau \cdot I_D}{C_{L\text{tot}}}$$

# Dynamic Error with Slewing

$$\Delta V_{oslew} = V_{ofinal} - \Delta V_{olin} \quad \Delta t_{slew} = (V_{ofinal} - \Delta V_{olin}) \cdot \frac{C_{Ltot}}{I_D}$$

- Using the above result, we can now calculate the dynamic error during the final linear settling portion

$$\text{For } t > \Delta t_{slew}: \quad v_o(t) = \Delta V_{oslew} + \Delta V_{olin}(1 - e^{-(t-\Delta t_{slew})/\tau})$$

$$\varepsilon_d(t) = \frac{v_o(t) - V_{final}}{V_{final}} = \frac{\Delta V_{oslew} + \Delta V_{olin}(1 - e^{-(t-\Delta t_{slew})/\tau}) - V_{ofinal}}{V_{ofinal}}$$

$$\varepsilon_d(t) = -\frac{\Delta V_{olin}}{V_{ofinal}} e^{-(t-\Delta t_{slew})/\tau}$$

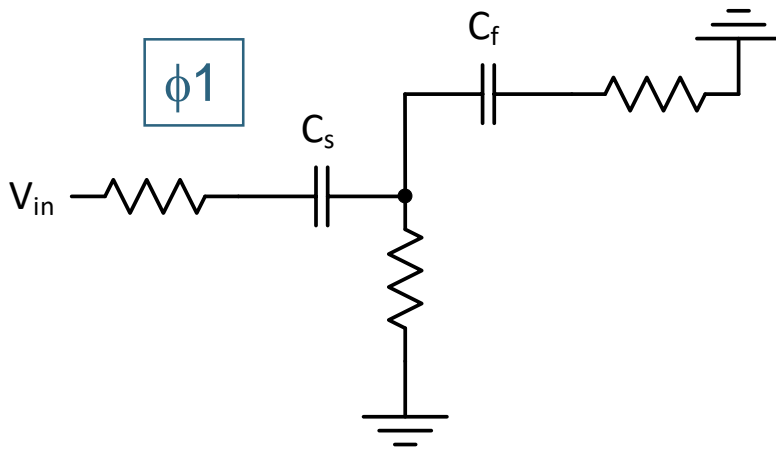


# **EE 240C**

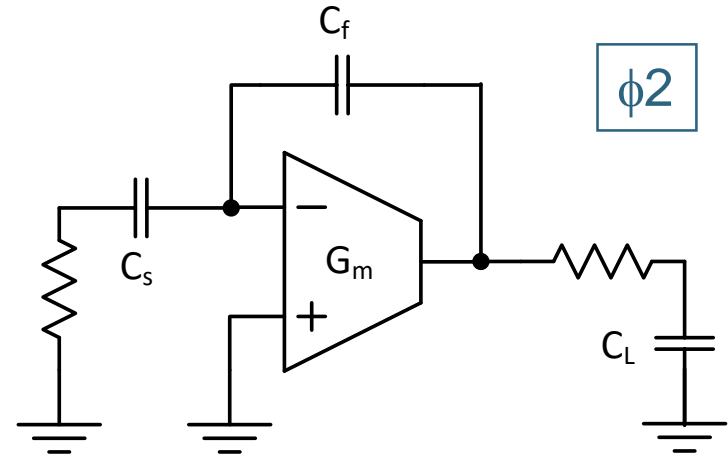
## **Analog-Digital Interface Integrated Circuits**

### **Track & Hold Amp – Noise**

# Noise Analysis

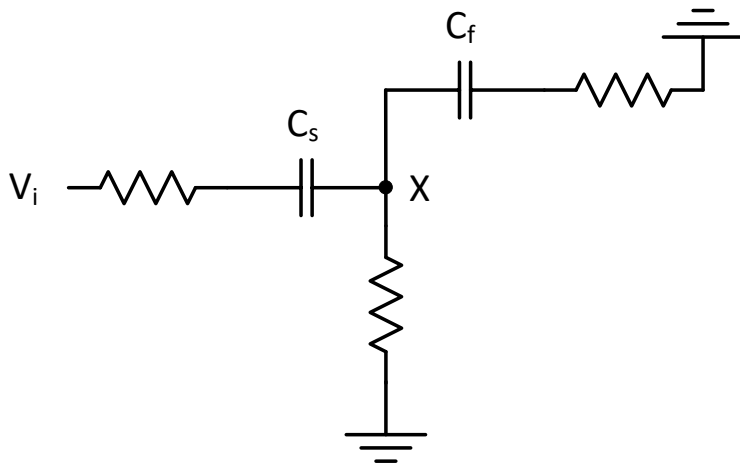


Noise due to switches



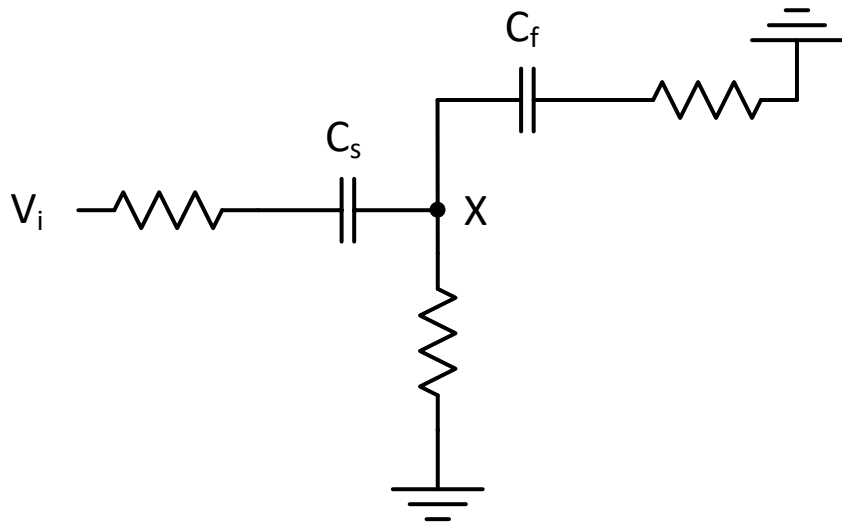
Noise due to amplifier and switches

# Tracking Phase ( $\phi_1$ )



- Variable of interest is total integrated "noise charge" at node X,  $q_x^2$
- Cumbersome to compute using standard analysis
  - Find transfer function from each noise source (3 resistors) to  $q_x$
  - Integrate magnitude squared expressions from zero to infinity and add
- Much easier
  - Use equipartition theorem

# Tracking Phase Noise Charge



- Energy stored at node X is

$$\frac{1}{2} \frac{q_x^2}{C_{\text{eff}}} = \frac{1}{2} \frac{q_x^2}{C_s + C_f}$$

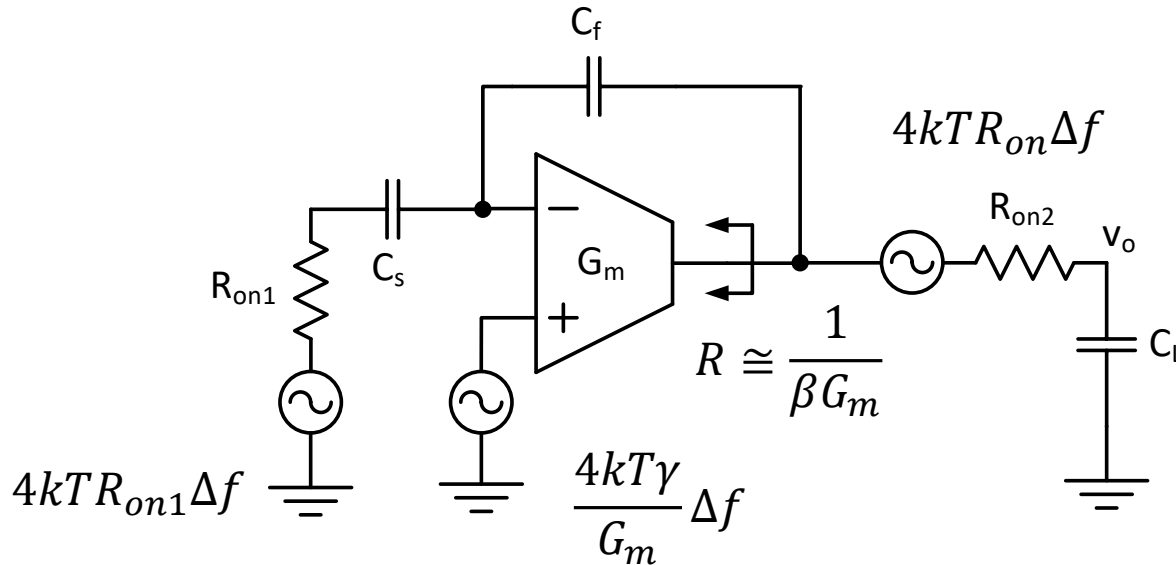
- Apply equipartition theorem

$$\overline{\frac{1}{2} \frac{q_x^2}{C_s + C_f}} = \frac{1}{2} kT$$

$$\overline{q_x^2} = kT(C_s + C_f)$$

- Note that any additional parasitic capacitance at node X will increase the sampled noise charge!

# Redistribution Phase Noise



( $\gamma$  includes excess noise from load,  $n_f$ )

- In a proper design,  $R_{on1}$  and  $R_{on2}$  will be much smaller than  $1/\beta G_m$ , else the switches would significantly affect the dynamics, which would be very wasteful
  - Switches with low on-resistance consume much less power than amplifiers with large  $G_m$

# Output Referred Noise Comparison

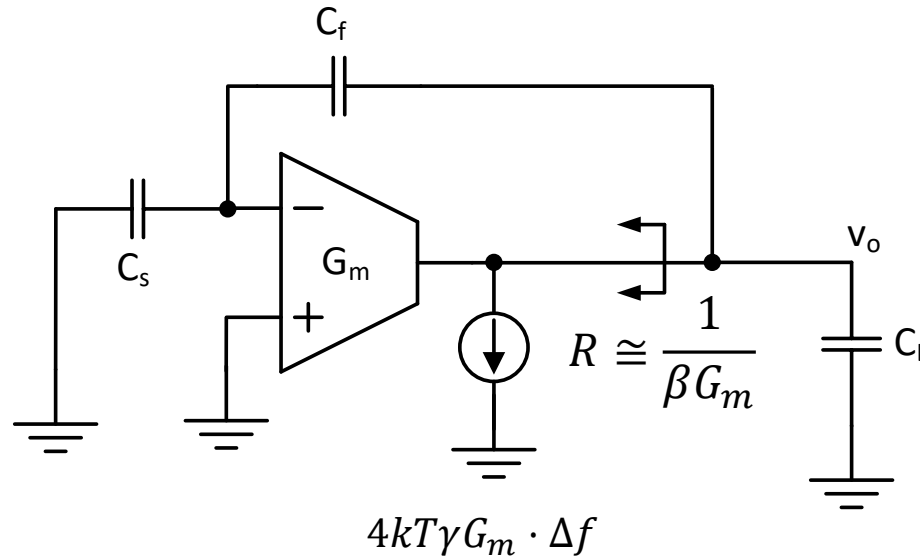
- $R_{on1}$  noise referred to  $v_o$   $N_1 = 4kTR_{on1}\Delta f \cdot \left(\frac{C_s}{C_f}\right)^2 \cdot |H(j\omega)|^2$
- $R_{on2}$  noise referred to  $v_o$   $N_2 = 4kTR_{on2}\Delta f \cdot |H(j\omega)|^2$
- Amplifier noise referred to  $v_o$   $N_a = \frac{4kT\gamma}{G_m}\Delta f \cdot \left(1 + \frac{C_s}{C_f}\right)^2 \cdot |H(j\omega)|^2$

$$\frac{N_a}{N_1} = \frac{\gamma}{G_m R_{on1}} \frac{\left(1 + \frac{C_s}{C_f}\right)^2}{\left(\frac{C_s}{C_f}\right)^2} \gg 1$$

$$\frac{N_a}{N_2} = \frac{\gamma}{G_m R_{on2}} \left(1 + \frac{C_s}{C_f}\right)^2 \gg 1$$

- Amplifier noise dominates over noise due to  $R_{on1}$ ,  $R_{on2}$

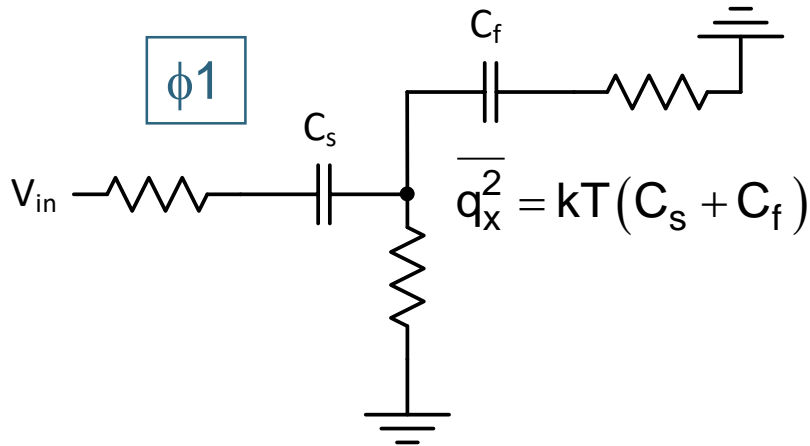
# Total Integrated Amplifier Noise



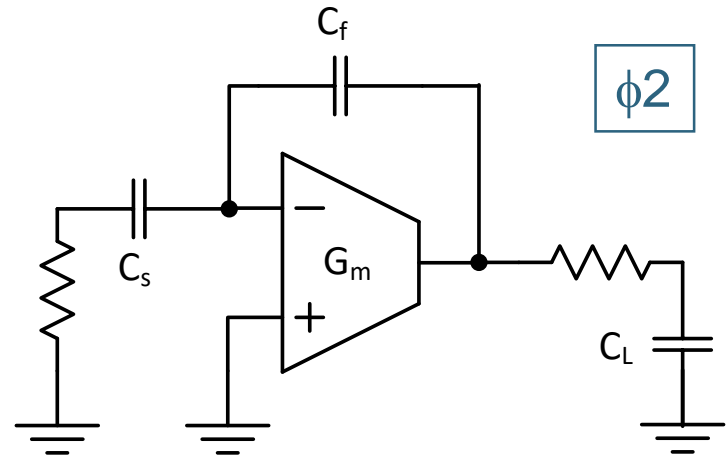
$$\overline{v_o^2} = 4kT\gamma \frac{1}{\beta R} \cdot \left| R \parallel \frac{1}{j\omega C_{Ltot}} \right|^2$$

$$\overline{v_o^2} = \int_0^\infty 4kT\gamma \frac{1}{\beta R} \cdot \Delta f \cdot \left| \frac{R}{1 + j\omega R C_{Ltot}} \right|^2 df = \gamma \frac{1}{\beta} \frac{kT}{C_{Ltot}}$$

# Adding up the Noise Contributions



$$\overline{v_{o,1}^2} = \frac{\overline{q_x^2}}{C_f^2} = kT \left( \frac{C_s + C_f}{C_f^2} \right) = \frac{kT}{C_f} \left( 1 + \frac{C_s}{C_f} \right)$$



$$\overline{v_{o,2}^2} \cong \gamma \frac{1}{\beta} \frac{kT}{C_{Ltot}}$$

$$\overline{v_{o,tot}^2} = \frac{kT}{C_f} \left( 1 + \frac{C_s}{C_f} \right) + \gamma \frac{1}{\beta} \frac{kT}{C_{Ltot}}$$



# Noise in Differential Circuits

---

- In differential circuits, the noise power is doubled (because there are two half circuits contributing to the noise)
- But, the signal power increases by 4x
  - Looks like a 3dB win?

$$DR_{\text{single}} \propto \frac{\hat{V}_o^2}{\frac{kT}{C}} \quad DR_{\text{diff}} \propto \frac{(2\hat{V}_o)^2}{2\frac{kT}{C}} = 2\frac{\hat{V}_o^2}{\frac{kT}{C}}$$

- Yes, there's a 3dB win in DR, but it comes at twice the power dissipation (due to two half circuits)
- Can get the same DR/power in a single ended circuit by doubling all cap sizes and  $g_m$
- But: beware of differential amplifiers with one input grounded!

# **EE 240C**

## **Analog-Digital Interface Integrated Circuits**

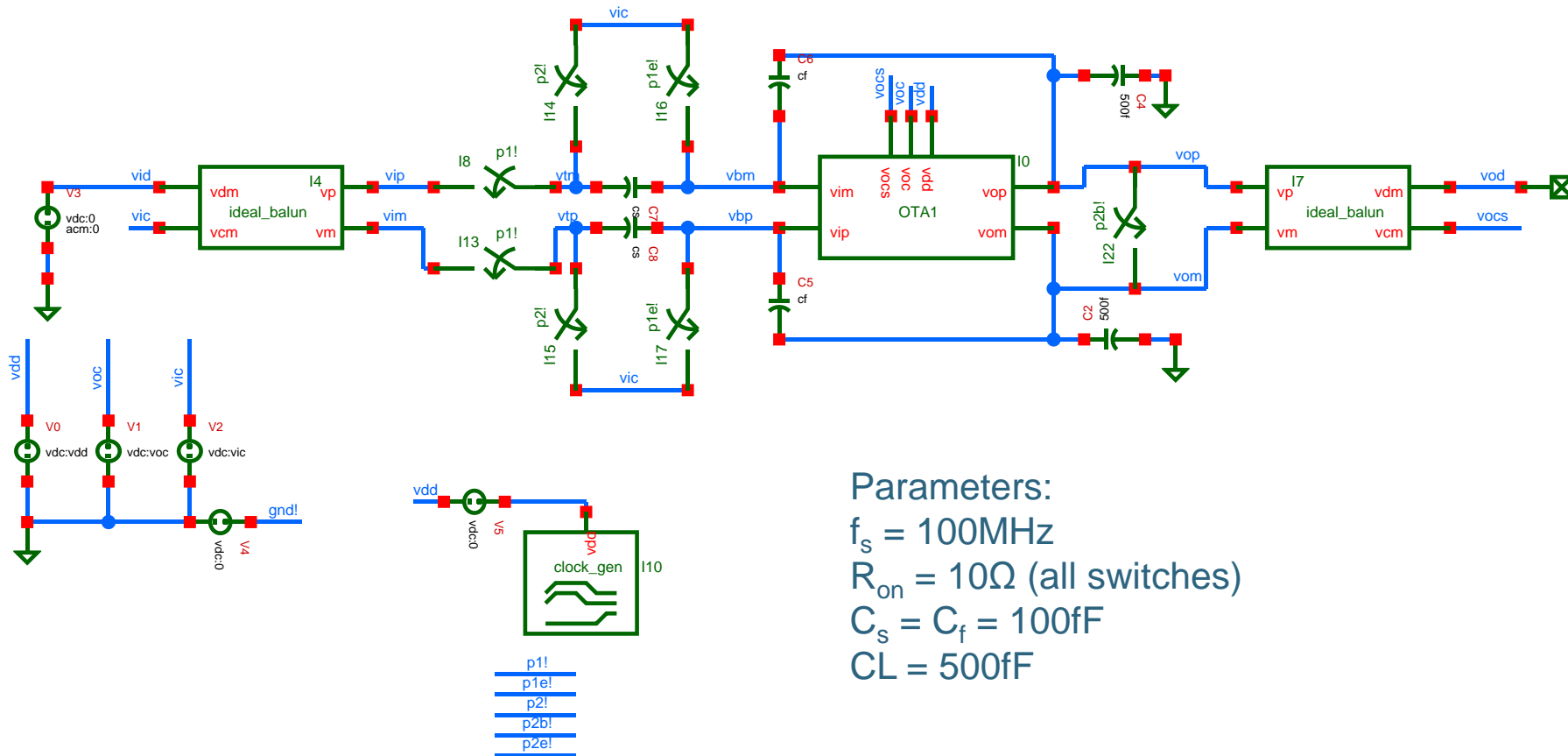
### **Track & Hold Amp – Noise Simulation**

# Noise Simulation Example

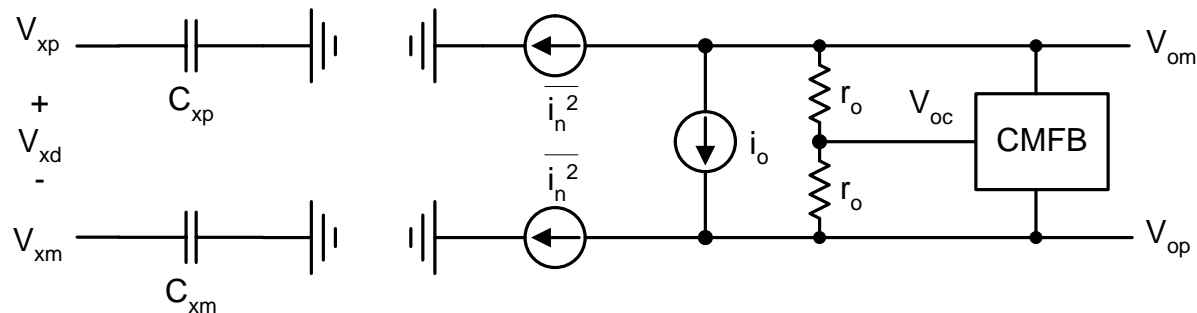
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- Three ways to simulate noise in switched capacitor circuits
- Basic .ac/.noise Spice simulations
  - Must simulate noise in each clock phase separately
    - Activate  $\phi 1$  switches, run .noise and integrate noise charge at relevant node over all frequencies and refer to output
    - Activate  $\phi 2$  switches, run .noise and integrate noise at output
- Periodic Steady State Simulation
  - E.g. SpectreRF or BDA, "periodic noise analysis" (PNOISE)
  - For linear time-variant circuits  $\rightarrow$  periodic clocked SC circuits
    - Noise from all phases is automatically added, all correlation taken care of
- Transient Noise
  - Simple setup

# Example Track and Hold Schematic



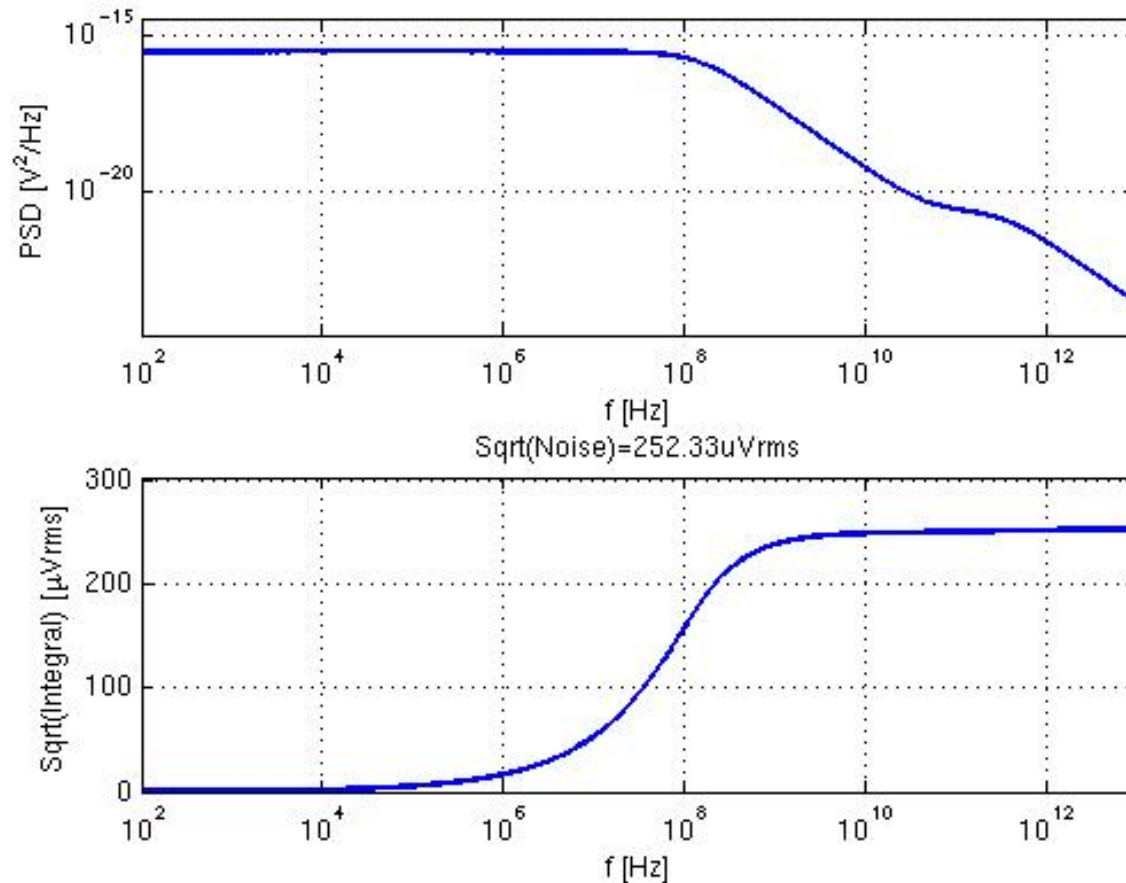
# OTA Simulation Model



$$C_{xp,m} = \frac{g_m}{2\pi f_T} \quad \frac{\overline{i_n^2}}{\Delta f} = \alpha \cdot kT g_m \quad r_o = \frac{a_{vo}}{g_m} \quad I_D = \frac{g_m}{(g_m / I_D)}$$

Parameters:  $g_m=1\text{mS}$ ,  $a_{vo}=1000$ ,  $\alpha=2$ ,  $g_m/I_D=10\text{S/A}$ ,  $f_T=20\text{GHz}$

# Hold Mode Noise Simulation (.noise)



Calculated value: 248 $\mu\text{Vrms}$

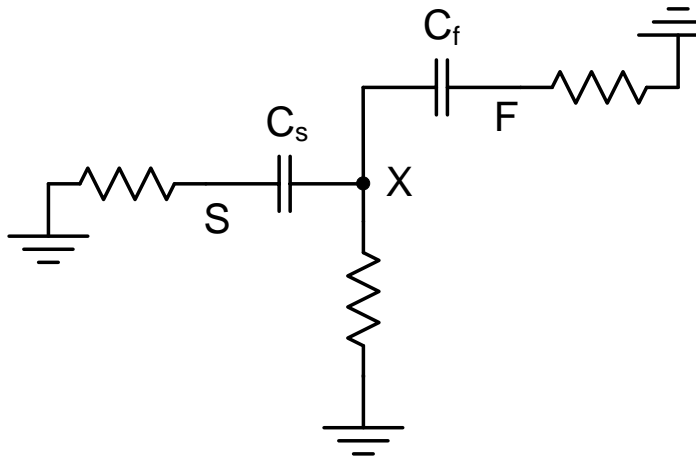
# Track Mode Noise Simulation (.noise)

\*\*\* Compute noise charge and refer charge referred to output via Cf

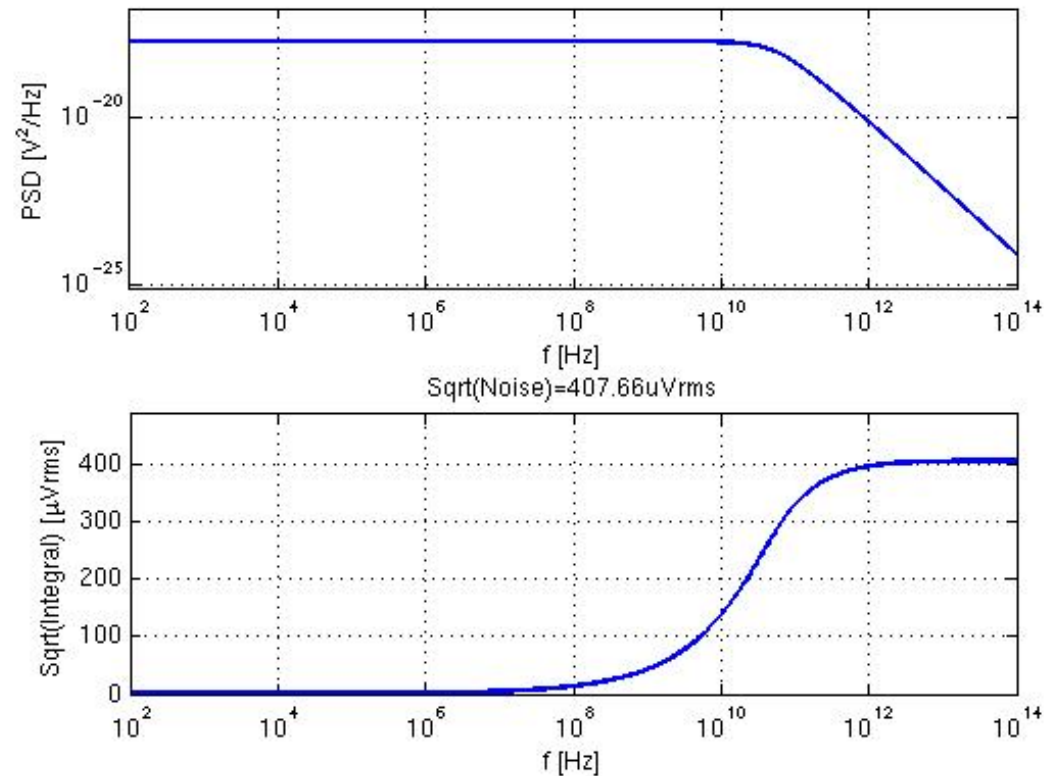
```
en vno 0 vcvs vol= `( cs*v(x,s) + cf*v(x,f) )/cf`
```

```
.ac dec 100 100 100Gig
```

```
.noise v(vno) vdummy
```



(shown single ended for simplicity)



Calculated value: 413uVrms

# PSS Setup

Analysis

Periodic Steady State Analysis

Engine

Fundamental Tones

#	Name	Expr	Value	Signal	SrcId
---	------	------	-------	--------	-------

Clear/Add Delete Update From Schematic

Beat Frequency 100M Auto Calculate

Beat Period

Output harmonics

Number of harmonics

Accuracy Defaults (errpreset)

conservative moderate liberal

Additional Time for Stabilization (tstab)

Save Initial Transient Results (saveinit)

no yes

Oscillator

Sweep

Enabled

Options...

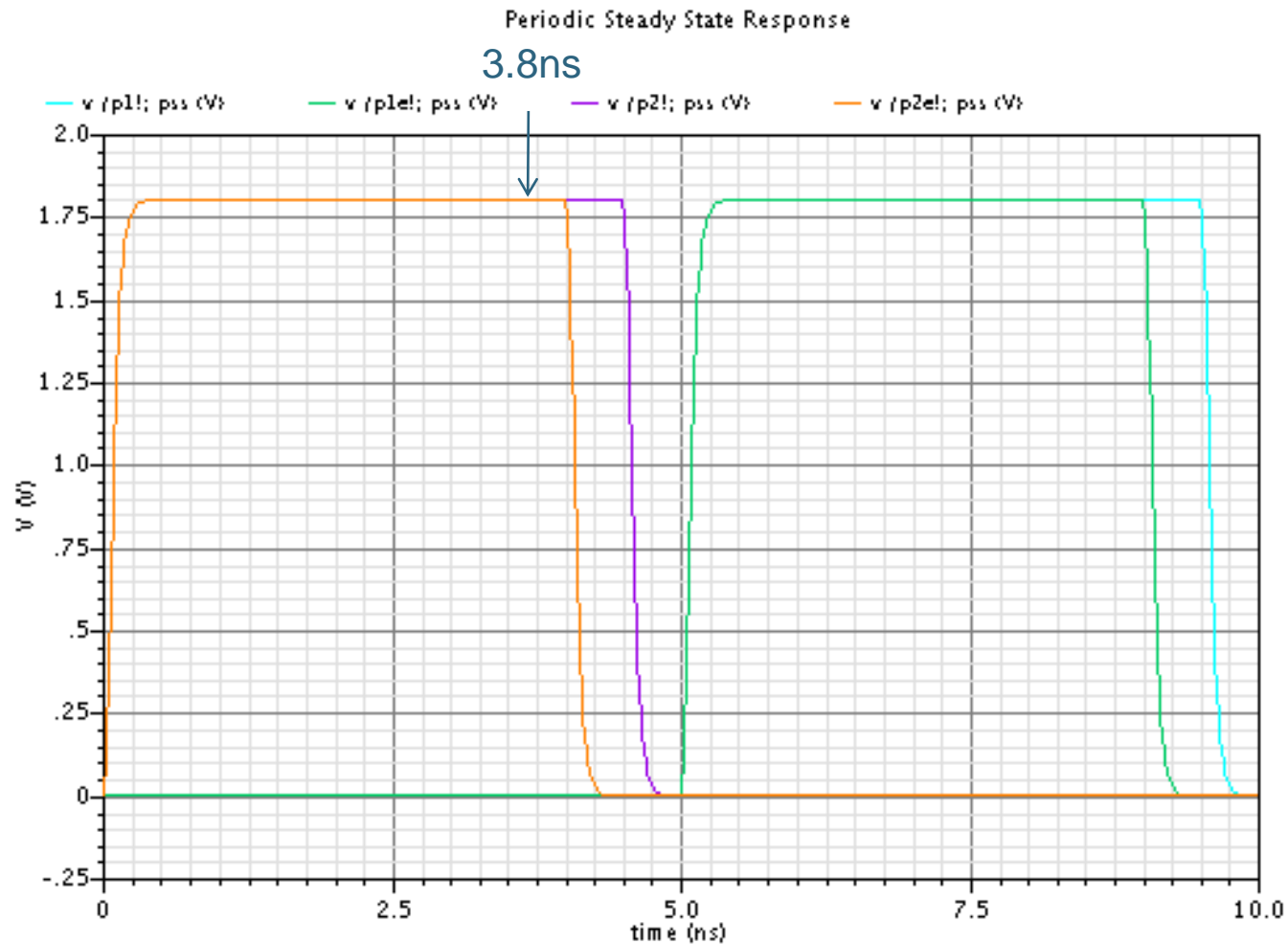
OK Cancel Defaults Apply Help

Use “tstab” if your circuit needs time to get into steady state (e.g. clock bootstrap circuits)

Important: set “maxacfreq” to the highest frequency at which you expect noise to be significant (10GHz in this example; see “Hold Mode Noise Simulation”)



# PSS Waveforms (Clocks)



# PNOISE Setup

The screenshot shows the PNOISE Setup dialog box with the following settings and annotations:

- PSS Beat Frequency (Hz):** 100M
- Sweep type:** default (dropdown), Sweep is Currently Absolute
- Output Frequency Sweep Range (Hz):**
  - Start-Stop (dropdown): Start 50, Stop 50e6
  - Sweep Type: Linear (dropdown)
  - Step Size (radio button): 40
  - Number of Steps (radio button): 40
- Add Specific Points:** ☐
- Sidebands:** Maximum sideband (dropdown): 100 (annotated with a blue arrow pointing to the value)
- Output:**
  - voltage (dropdown)
  - Positive Output Node: /v<sub>o</sub>d (text box), Select button
  - Negative Output Node: /gnd! (text box), Select button
- Input Source:**
  - voltage (dropdown)
  - Input Voltage Source: /v<sub>A</sub> (text box), Select button
- Reference side-band:** Enter in field (dropdown): 0 (text box)
- Noise Type:** timedomain (dropdown) (annotated with a blue arrow pointing to the dropdown menu)
- timedomain: strobed noise analysis**
- Noise Skip Count:** ☐
- Number of Points:** ☒ 0
- Add Specific Points:** ☒ 3.8n (text box) (annotated with a blue arrow pointing to the value)
- Enabled:** ☒
- Buttons:** OK, Cancel, Defaults, Apply, Help

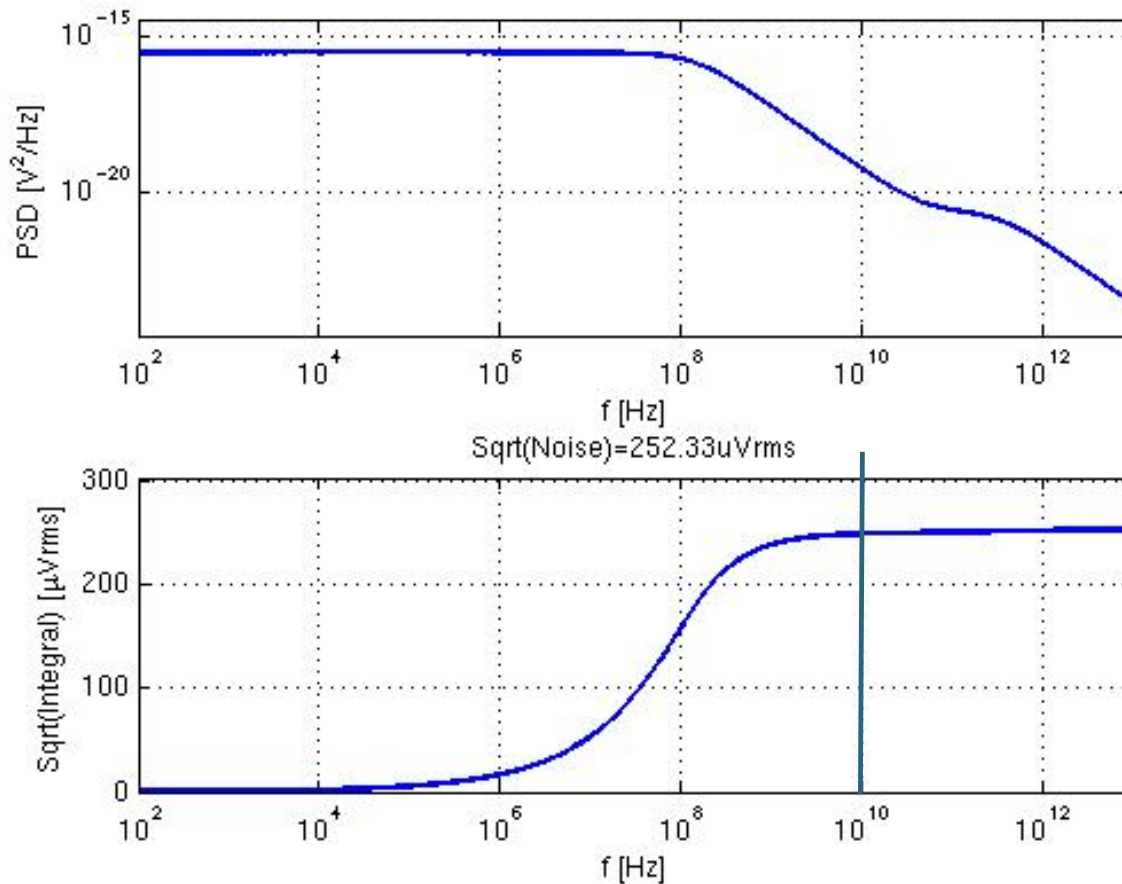
“Number of sidebands” – typically ~20...200 to handle noise folding properly. Fast switches → more sidebands needed. Again, Be sure to set “maxacfrequency” in the PSS analysis options to a correspondingly large value. Note: This is not a problem in some simulators such as BDA, which cover an “infinite” number of sidebands

“timedomain” means simulator computes spectrum of discrete time noise samples

Sampling instant (3.8ns in this example)

# How Many Sidebands are Needed? (1)

Hold mode noise integral (.noise)



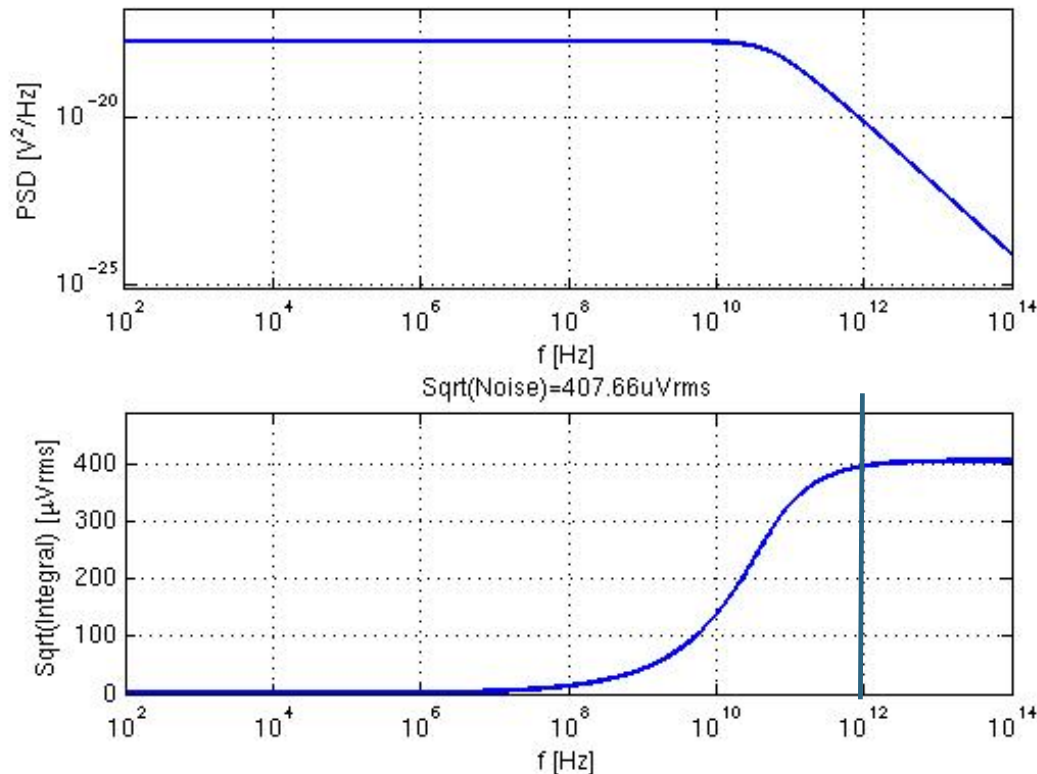
Noise up to 10GHz must be considered !

→ numsidebands = 100

→ maxacfreq = 10GHz,

# How Many Sidebands are Needed? (2)

Track mode noise integral, (.noise,  $R_{on} = 10$  Ohms)

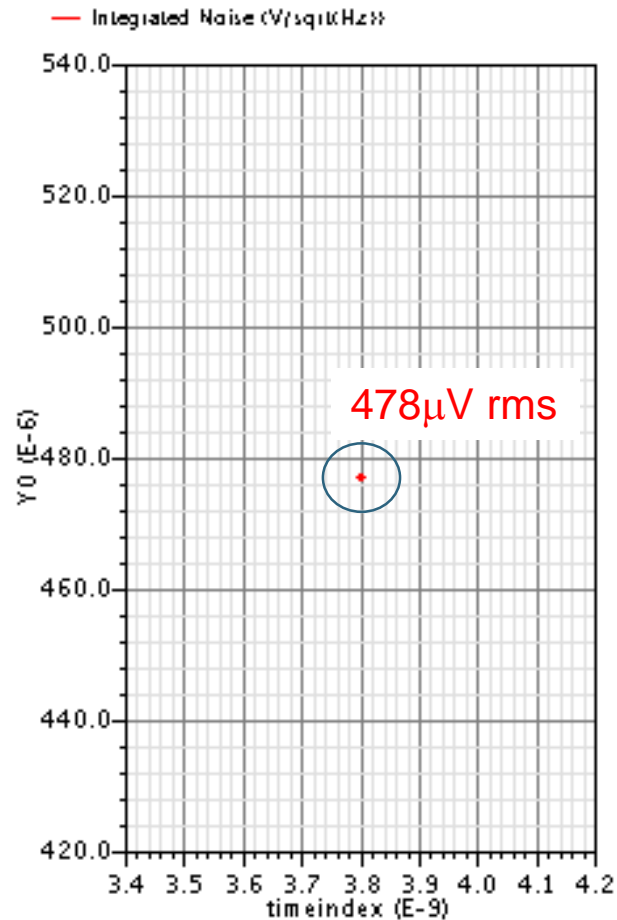


Noise up to 1 THz must be considered !

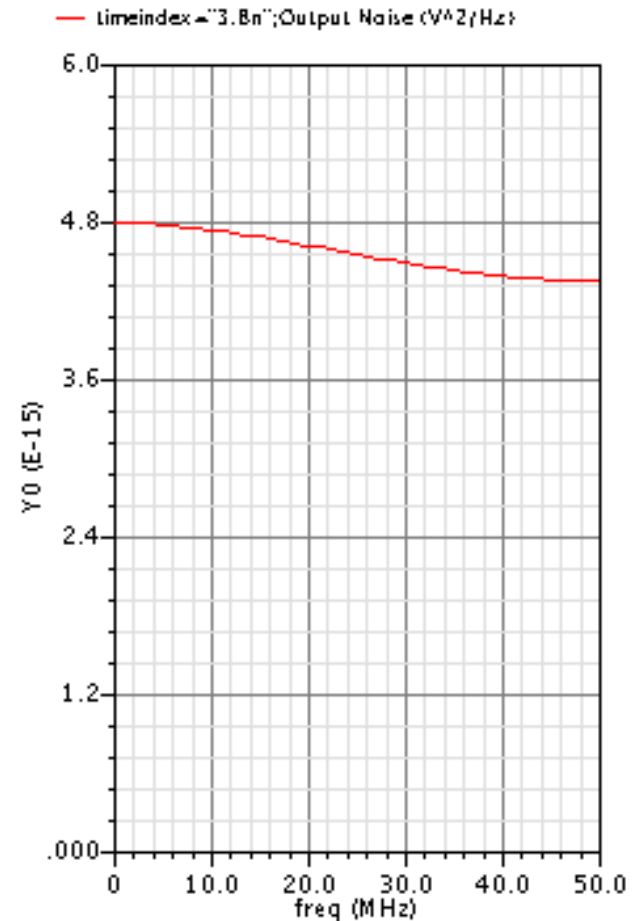
→ numsidebands = 10,000?  
No! Increase  $R_{on}$  to maintain reasonable simulation time.  
Keep  $R_{on}C \sim 10\times$  faster than amplifier.

# PNOISE Result

## Sampled Noise



## Noise PSD



# Comparison

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Calculated:  $\overline{v_{o,1}^2} = (413\mu\text{Vrms})^2$      $\overline{v_{o,2}^2} = (248\mu\text{Vrms})^2$      $\overline{v_{o,\text{tot}}^2} = (482\mu\text{Vrms})^2$

Simulated:  
(.noise)  $\overline{v_{o,1}^2} = (415\mu\text{Vrms})^2$      $\overline{v_{o,2}^2} = (252\mu\text{Vrms})^2$      $\overline{v_{o,\text{tot}}^2} = (485\mu\text{Vrms})^2$

Simulated:  
(PNOISE)  $\overline{v_{o,\text{tot}}^2} = (478\mu\text{Vrms})^2$

- Very good agreement between calculation and both simulation approaches

# Summary – Sampling Circuits

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- Implementation styles
  - Purely passive
  - Charge redistribution or flip-around architecture
    - Input common-mode rejection & gain > 1 vs increased feedback factor
- In a properly designed circuit only the most fundamental issues are significant
  - Jitter,  $kT/C$  noise
- Charge injection is not a problem if properly handled
  - E.g. through bottom plate sampling

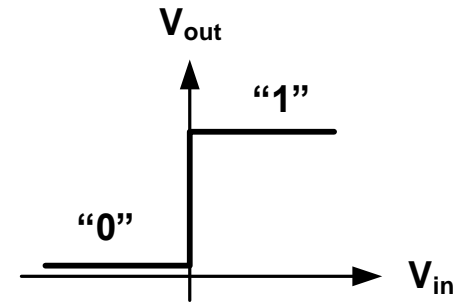
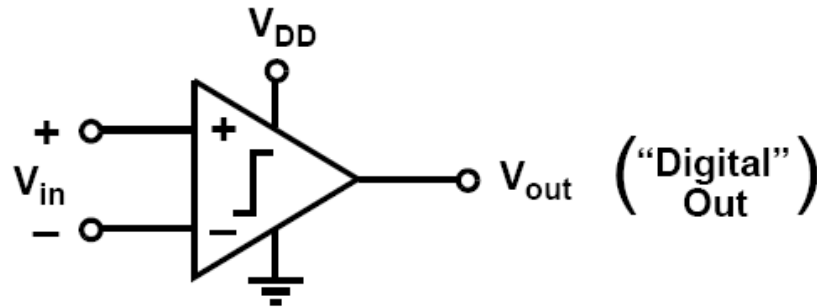
# **EE 240C**

## **Analog-Digital Interface Integrated Circuits**

### **Comparators**



# Ideal Voltage Comparator



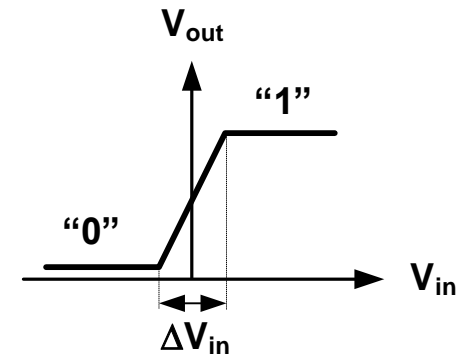
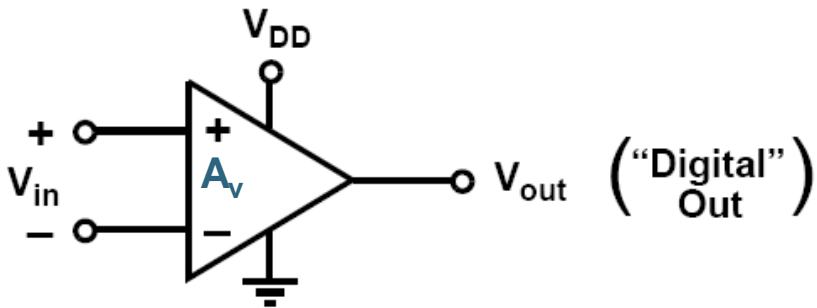
- Function
  - Compare the instantaneous values of two analog voltages (e.g. an input signal and a reference voltage) and generate a digital 1 or 0 indicating the polarity of that difference

# Design Considerations

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- Accuracy
  - Gain (resolution)
  - Offset
- Speed
  - Small-signal bandwidth
  - Settling time or delay time, slew rate
  - Overdrive recovery
- Power dissipation
- Input properties
  - Sampled data versus continuous time
  - Common-mode rejection
  - Input capacitance and linearity of input capacitance
  - Kickback noise

# Gain Requirements



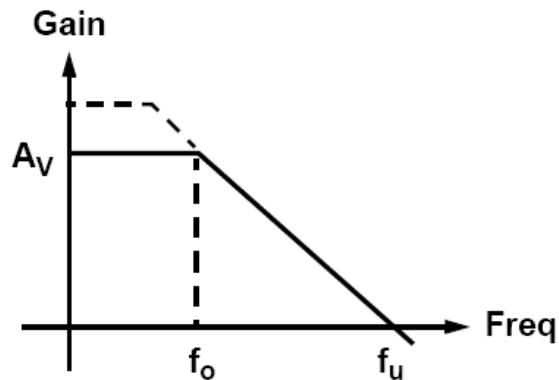
$$\Delta V_{in} = \frac{V_{DD}}{A_{vo}}$$

- E.g. 12-bit ADC,  $V_{DD}=1.8V$ ,  $FSR=0.9V \Rightarrow LSB=0.9V/4096$
- For 1/2 LSB precision, we need

$$A_v = \frac{1.8V}{0.5 \cdot 0.9V/4096} \cong 16,000 = 84dB$$

# How about Using an OpAmp or OTA?

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$f_u$  = unity gain frequency,  $f_o$  = - 3dB frequency

# How to Implement High Gain?

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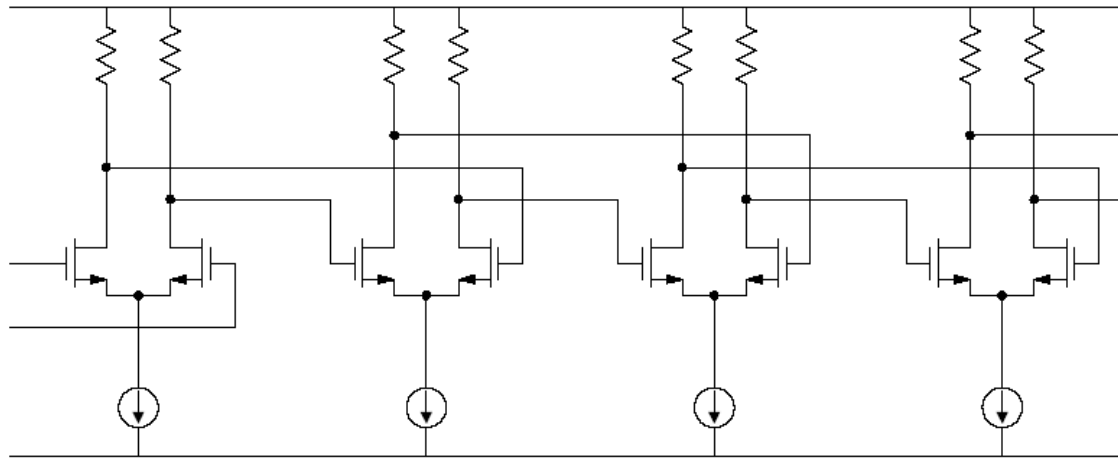
- Considerations
  - Amplification need not be linear
  - Amplification need not be continuous in time, if comparator is used in a sampled data system
    - Clock signal will tell comparator when to make a decision
- Implementation options
  - Single stage amplification
    - E.g. OTA or OpAmp in open loop configuration
  - Multi-stage amplification
    - E.g. cascade of resistively loaded differential pairs
  - Regenerative latch using positive feedback
    - E.g. cross coupled inverters

# **EE 240C**

## **Analog-Digital Interface Integrated Circuits**

### **Comparators – Cascade of Amplifiers**

# Cascade of Open-Loop Amplifiers



In each stage:  $\omega_u = \frac{g_m}{C_{gs}} \cong \text{const.}$        $A_0 = g_m R = \frac{\omega_u}{\omega_0}$        $\omega_0 = \frac{1}{RC} = \frac{\omega_u}{A_0}$

- Possible choices for a given, constant overall gain objective
  - Lots of stages with low gain
  - Only a few stages with moderate gain

# Bandwidth Perspective

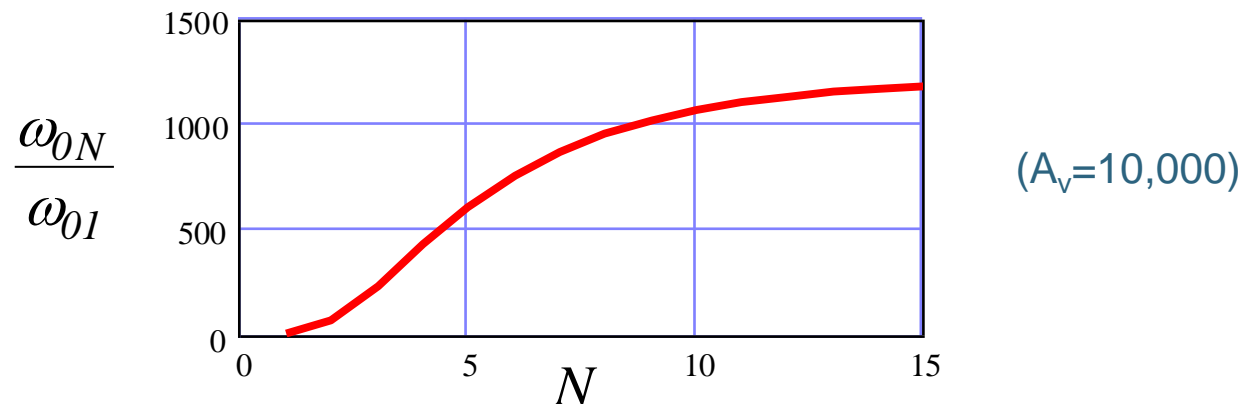
- If we only care about small signal bandwidth, it follows that we should cascade many low gain stages
  - Makes intuitive sense, because each individual stage will have a very large bandwidth
- Detailed analysis shows (for fixed  $\omega_u$ )

$$\frac{\omega_{0N}}{\omega_{01}} = A_v^{\left(\frac{N-1}{N}\right)} \sqrt{2^{\frac{1}{N}} - 1}$$

$A_v$  Total gain requirement

$\omega_{01}$  Bandwidth of single stage realization

$\omega_{0N}$  Bandwidth of N stage realization





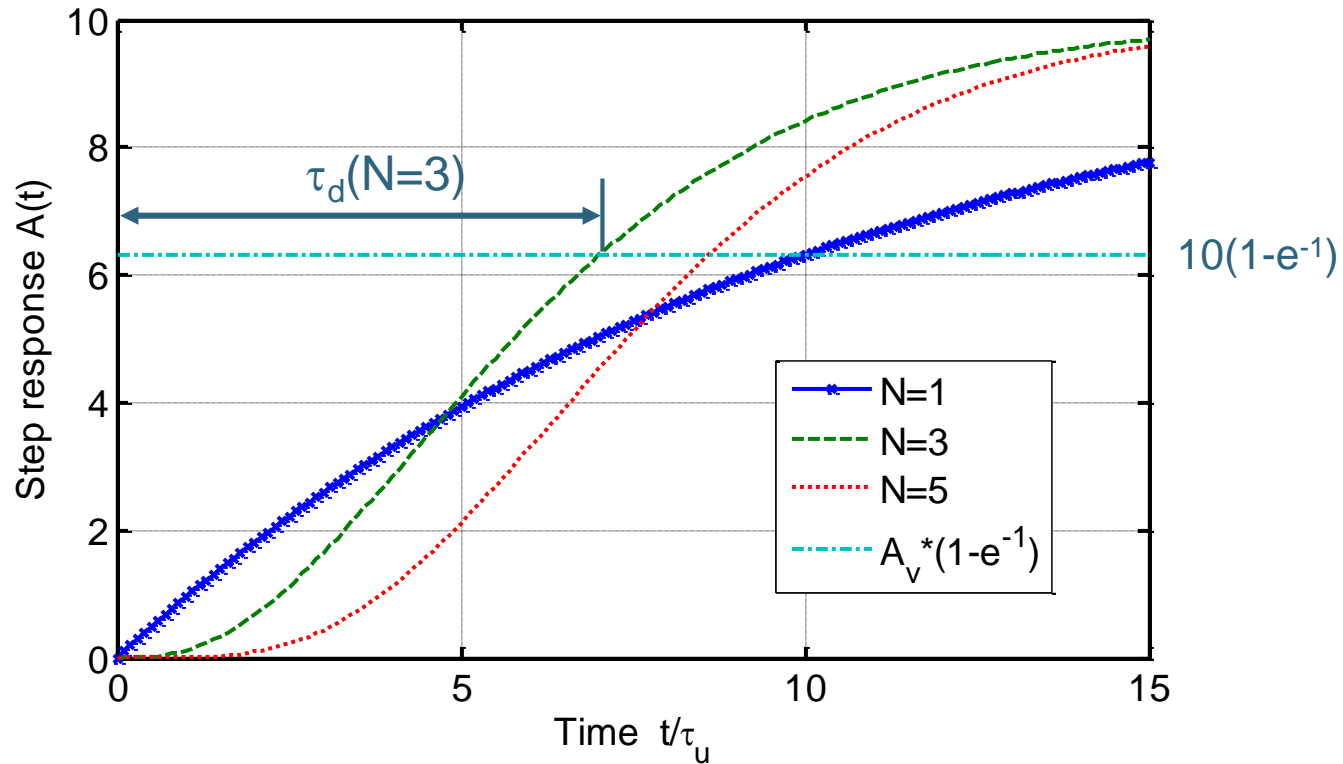
# Step Response (1)

- When the input is a sampled data signal, it is more important to minimize the delay in response to an input step

$$V_{\text{out}}(s) = V_{\text{in}}(s)A(s) = \frac{V_{\text{istep}}}{s} \frac{A_v}{(1 + s \cdot \tau_u A_v^{1/N})^N} \quad \tau_u = \frac{1}{\omega_u} \quad A_v = A_0^N$$

$$V_{\text{out}}(t) = V_{\text{istep}} A_v \underbrace{\left( 1 - e^{-\frac{t}{\tau_u A_v^{1/N}}} \sum_{i=0}^{N-1} \frac{\left( \frac{t}{\tau_u A_v^{1/N}} \right)^i}{i!} \right)}_{A(t)}$$

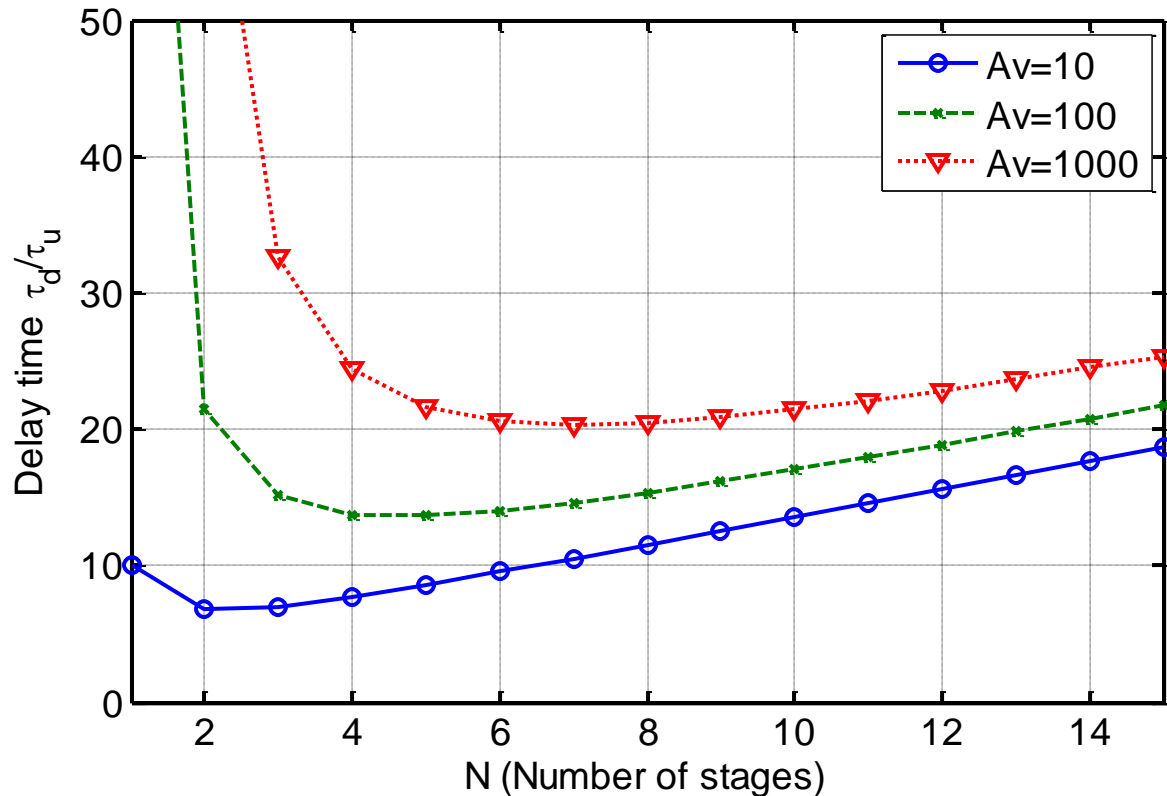
# Step Response (2)



- Three stage amplifier wins! (for  $A_v=10$ )

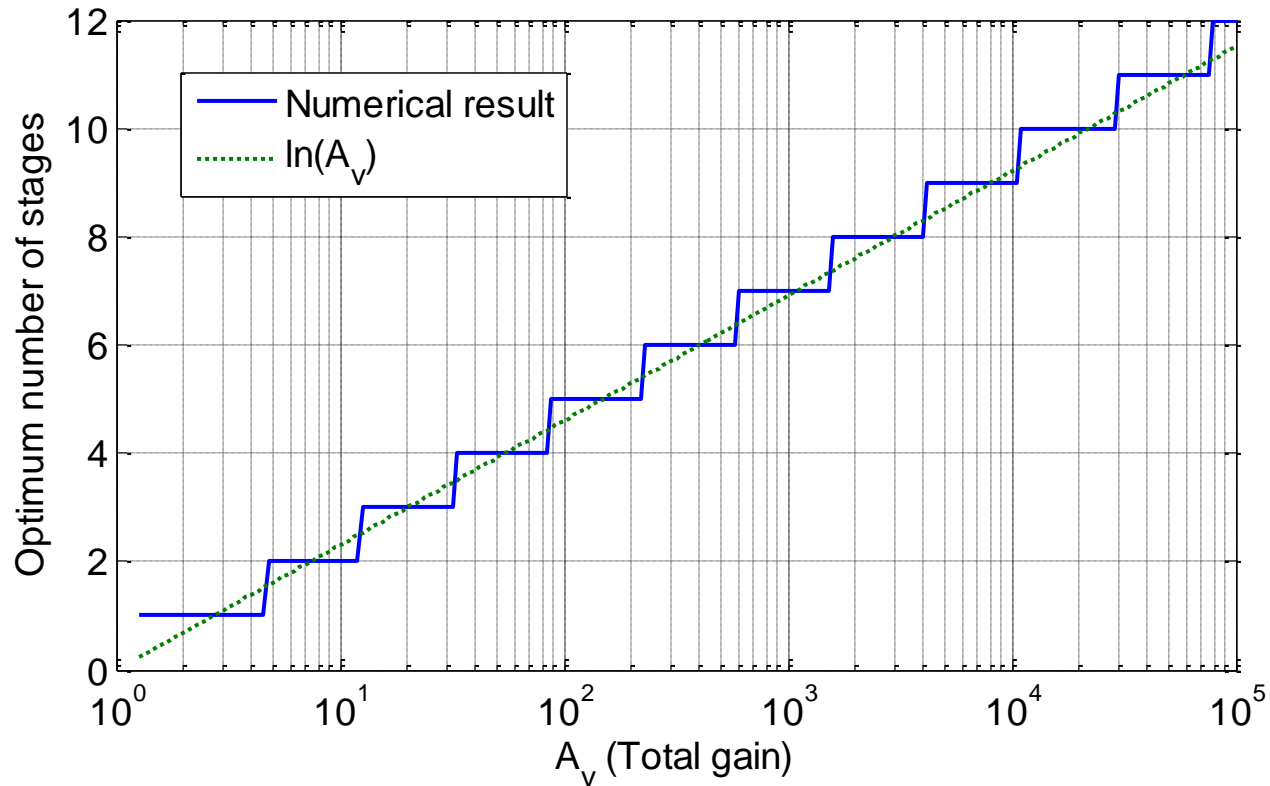
# Delay versus Number of Stages

$$A(\tau_d) = A_v(1 - e^{-1}) \Rightarrow \tau_d \quad (\text{numerically})$$



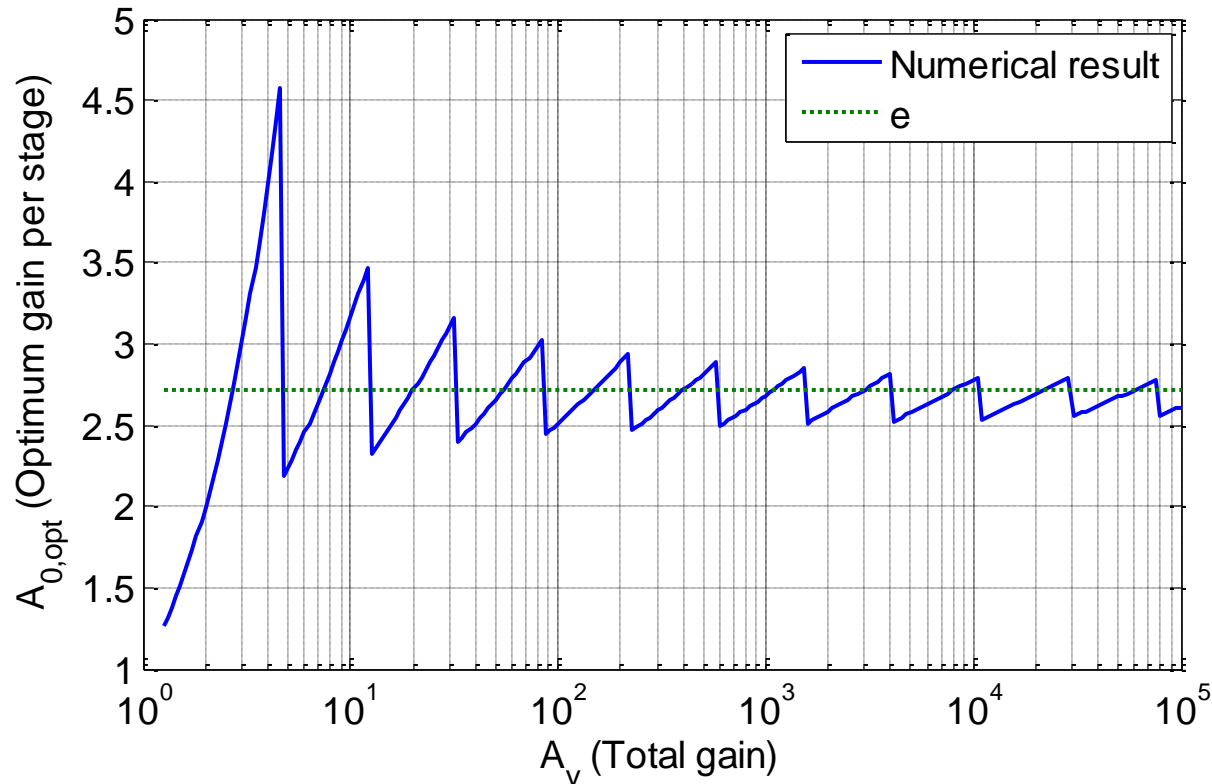
- Shallow minima!

# Optimum Number of Stages



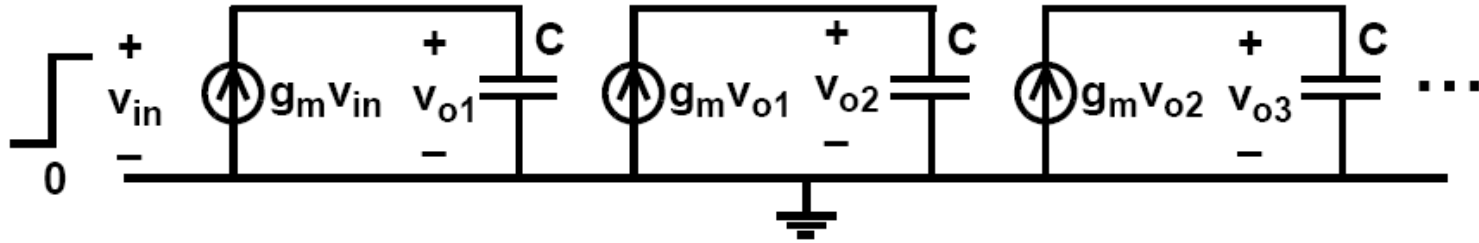
$$N_{opt} \cong \ln(A_v)$$

# Optimum Gain per Stage



$$N_{opt} \cong \ln(A_v) \quad e^{N_{opt}} \cong A_v = A_{0,opt}^{N_{opt}} \Rightarrow A_{0,opt} \cong e$$

# Cascade of "Integrators" (1)



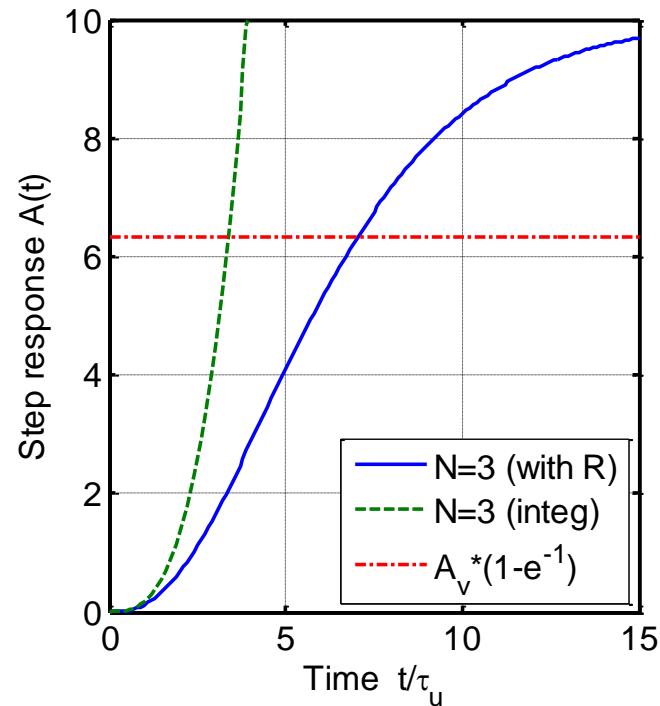
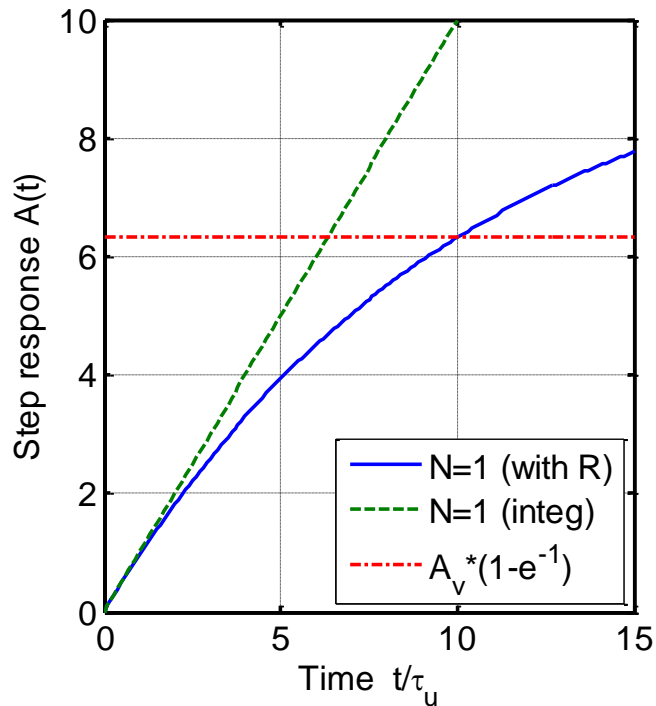
- Intuition
  - Load resistors (in cascade of open loop amplifiers) shunt current away from load capacitance; this slows down amplification
  - Drop assumption  $A_v = A_0^N$  to see what happens...
- Analysis

$$v_{o1} = \frac{g_m}{sC} v_{in} = \frac{\omega_u}{s} v_{in} \quad v_{oN} = \frac{\omega_u^N}{s^N} v_{in}$$

# Cascade of "Integrators" (2)

$$V_{out}(s) = \frac{V_{istep}}{s} \frac{\omega_u^N}{s^N}$$

$$V_{out}(t) = V_{istep} \cdot \omega_u^N \frac{t^N}{N!}$$



# Cascade of "Integrators" (3)

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- Cascade of integrators achieves faster amplification than cascade of resistively loaded stages
- Delay time

$$\tau_d = \tau_u [(N! \cdot A(\tau_d))]^{1/N} \quad A(\tau_d) = \frac{V_{\text{out}}(\tau_d)}{V_{\text{instep}}}$$

- Optimum number of stages approximately given by

$$N_{\text{opt}} = 1.1 \ln[A(\tau_d)] + 0.79 \quad [\text{Wu, JSSC 12/1988}]$$

- Effective gain per stage is still relatively close to  $e=2.7183\dots$